

# TPS65150-Q1 具备栅极电压整形功能和 VCOM 缓冲器的汽车 LCD 电源，适用于源极和栅极驱动器

## 1 特性

- 符合 AEC-Q100 标准：的顶部
  - 器件温度 1 级：-40°C 至 125°C 结温范围
  - 器件人体放电模型 (HBM) 静电防护 (ESD) 分类符合 AEC - Q100-002
  - 器件带电器件模型 (CDM) ESD 分类符合 AEC-Q100-011
- 输入电压范围：1.8V 至 6V
- $V_{(VS)}$  升压转换器
  - 输出电压高达 15V
  - 输出电压精度 < 1%
  - 2A 开关电流限值
- $V_{(VGH)}$  正向稳压电荷泵驱动器
  - 输出电压高达 30 V
  - 栅极电压整形
- $V_{(VGL)}$  负向稳压电荷泵驱动器
  - 输出电压低至 -15V
- 集成 VCOM 缓冲器
- 可调上电序列
  - 外部隔离 MOSFET 的栅极驱动信号，针对  $V_{(VS)}$
- DRV8303 中的 特性
  - 超出稳压范围保护
  - 过压保护
  - 可调故障检测时序
  - 热关断
- 带有外露散热焊盘的 24 引脚 TSSOP 封装

## 2 应用

- 4" 至 17"液晶 (LCD) 显示屏
  - 汽车信息娱乐系统和仪表盘
  - 汽车导航系统
  - 后座娱乐系统
  - 智能车镜

## 3 说明

TPS65150-Q1 是一款电源，适用于汽车 LCD 应用。该器件集成了一个针对源极电压的升压转换器以及两个针对栅极电压并经过稳压的可调节电荷泵驱动器。为了削减外部成本、改善图像质量并减少影像残留，该器件采用 VCOM 缓冲器并具备栅极电压整形功能。

该器件经设计可由 1.8V 至 6V 的电源供电运行，非常适合使用 3.3V 或 5V 固定输入电压轨的汽车 LCD 应用。

VGL 和 VGH 的可调上电序列允许该器件针对各种显示屏进行优化。

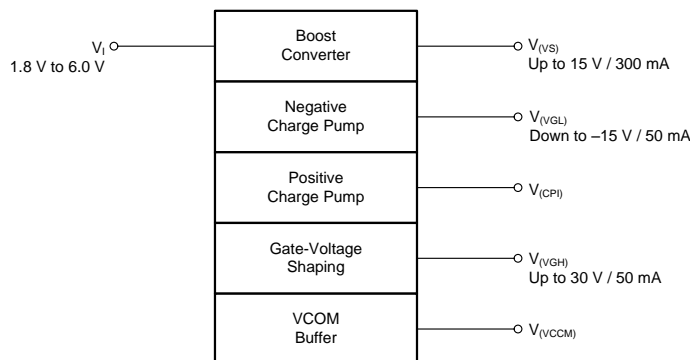
为了防止系统发生故障，TPS65150-Q1 集成了可调节关断锁存功能。该器件监测输出 ( $V_{(VS)}$ 、 $V_{(VGL)}$  和  $V_{(VGH)}$ )。当其中一个输出低于其电源正常阈值的时间超过可调节故障延迟时间后，该器件进入关断模式。

### 器件信息<sup>(1)</sup>

器件型号	封装	封装尺寸 (标称值)
TPS65150-Q1	TSSOP (24)	6.40mm x 7.80mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

### 框图



## 目录

1	特性 .....	1	7.4	Device Functional Modes .....	20
2	应用 .....	1	<b>8</b>	<b>Application and Implementation</b> .....	<b>22</b>
3	说明 .....	1	8.1	Application Information .....	22
4	修订历史记录 .....	2	8.2	Typical Application .....	22
<b>5</b>	<b>Pin Configuration and Functions</b> .....	<b>3</b>	8.3	System Examples .....	30
<b>6</b>	<b>Specifications</b> .....	<b>5</b>	<b>9</b>	<b>Power Supply Recommendations</b> .....	<b>33</b>
6.1	Absolute Maximum Ratings .....	5	<b>10</b>	<b>Layout</b> .....	<b>33</b>
6.2	ESD Ratings .....	5	10.1	Layout Guidelines .....	33
6.3	Recommended Operating Conditions .....	5	10.2	Layout Example .....	34
6.4	Thermal Information .....	5	<b>11</b>	<b>器件和文档支持</b> .....	<b>35</b>
6.5	Electrical Characteristics .....	6	11.1	器件支持 .....	35
6.6	Switching Characteristics .....	7	11.2	接收文档更新通知 .....	35
6.7	Typical Characteristics .....	8	11.3	社区资源 .....	35
<b>7</b>	<b>Detailed Description</b> .....	<b>10</b>	11.4	商标 .....	35
7.1	Overview .....	10	11.5	静电放电警告 .....	35
7.2	Functional Block Diagram .....	11	11.6	Glossary .....	35
7.3	Feature Description .....	12	<b>12</b>	<b>机械、封装和可订购信息</b> .....	<b>35</b>

## 4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

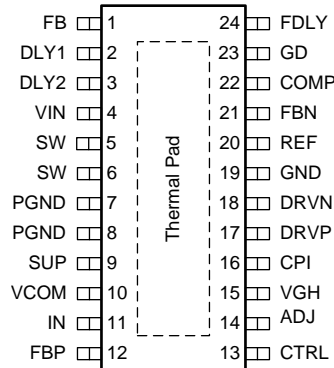
Changes from Revision B (December 2016) to Revision C	Page
• 已将“符合 AEC-Q100 标准”移动到特性列表 .....	1
• Changed the <i>Electrical Characteristics</i> conditions From: $T_A = -40^{\circ}\text{C}$ to $85^{\circ}\text{C}$ To: $T_A = -40^{\circ}\text{C}$ to $125^{\circ}\text{C}$ .....	6

Changes from Revision A (September 2013) to Revision B	Page
• 已添加 <i>ESD</i> 额定值表，特性 说明部分、器件功能模式、应用和实施部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分 .....	1
• Added specifications to the <i>Absolute Maximum Ratings</i> table .....	5
• 已添加 <i>Switching Characteristics</i> .....	7
• 已更改 typical characteristics graphs .....	8
• 已更改 <i>Functional Block Diagram</i> for clarity .....	11

Changes from Original (June 2013) to Revision A	Page
• 已更改 文档状态“产品预览”至“量产数据” .....	1

## 5 Pin Configuration and Functions

**PWP Package  
24-Pin TSSOP  
Top View**



**Pin Functions**

PIN		I/O	DESCRIPTION
NAME	HTSSOP		
ADJ	14	I/O	Gate voltage shaping circuit. Connecting a capacitor to this pin sets the fall time of the positive gate voltage $V_{(VGH)}$ .
COMP	22	O	This is the compensation pin for the main boost converter. A small capacitor and if required a series resistor is connected to this pin.
CPI	16	I	Input of the VGH isolation switch and gate voltage shaping circuit.
CTRL	13	I	Control signal for the gate voltage shaping signal. Apply the control signal for the gate voltage control. Usually the timing controller of the LCD panel generates this signal. If this function is not required, this pin must be connected to $V_I$ . By doing this, the internal switch between CPI and VGH provides isolation for the positive charge pump output $V_{(VGH)}$ . DLY2 sets the delay time for $V_{(VGH)}$ to come up.
DLY1	2	I/O	Power-on sequencing adjust. Connecting a capacitor from this pin to ground allows to set the delay time between the boost converter output $V_{(VS)}$ and the negative charge pump $V_{(VGL)}$ during start-up.
DLY2	3	I/O	Power-on sequencing adjust. Connecting a capacitor from this pin to ground allows to set the delay time between the negative charge pump $V_{(VGL)}$ and the positive charge pump during start-up. Note that Q5 in the gate voltage shaping block only turns on when the positive charge pump is within regulation. (This provides input-output isolation of $V_{(VGH)}$ ).
DRVN	18	I/O	Negative charge pump driver.
DRVP	17	I/O	Positive charge pump driver.
FB	1	I	Boost converter feedback sense input.
FBN	21	I	Negative charge pump feedback sense input.
FBP	12	I	Positive charge pump feedback sense input.
FDLY	24	I/O	Fault delay. Connecting a capacitor from this pin to $V_I$ sets the delay time from the point when one or more of the of the outputs $V_{(VS)}$ , $V_{(VGH)}$ , $V_{(VGL)}$ drops below its power good threshold until the device shuts down. To restart the device, the input voltage must be cycled to ground. This feature can be disabled by connecting the FDLY pin to $V_I$ .
GD	23	I	Active-low, open-drain output. This output is latched low when the boost converter output is in regulation. This signal can be used to drive an external MOSFET to provide isolation for $V_{(VS)}$ .
GND	19		Analog ground.
IN	11	I	Input of the VCOM buffer. If this pin is connected to ground, the VCOM buffer is disabled.
PGND	7, 8		Power ground.
REF	20	O	Internal reference output, typically 1.213 V.
SUP	9	I/O	Supply pin of the positive, negative charge pump and boost converter gate drive circuit. This pin must be connected to the output of the main boost converter and cannot be connected to any other voltage rail.

**Pin Functions (continued)**

PIN		I/O	DESCRIPTION
NAME	HTSSOP		
SW	5, 6	I	Switch pin of the boost converter.
VCOM	10	O	VCOM buffer output. Typically a 1- $\mu$ F output capacitor is required on this pin.
VGH	15	O	Positive output voltage to drive the TFT gates with an adjustable fall time. This pin is internally connected with a MOSFET switch to the positive charge pump input CPI.
VIN	4	I	This is the input voltage pin of the device.
Thermal Pad	—		The thermal pad must to be soldered to GND

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)(2)</sup>

		MIN	MAX	UNIT
Voltages on pin	VIN, CTRL	-0.3	7	V
	ADJ	-0.3	22	V
	VCOM, IN, DRVP, DRVN	-0.3	15	V
	FBN, COMP, FBP, FB, DLY1, DLY2	-0.3	5.5	V
	REF	-0.3	4	V
	VGH	-0.3	30	V
	FDLY	-0.3	6	V
	GD, SUP	-0.3	15.5	V
	SW	-0.3	20	V
	CPI	-0.3	32	V
Operating junction temperature, T <sub>J</sub>		-40	125	°C
Storage temperature, T <sub>stg</sub>		-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to network ground terminal.

### 6.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discharge	Human-body model (HBM), per AEC-Q100-02	±2000	V
	Charged-device model (CDM), per AEC-Q100-011	±500	

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V <sub>I</sub>	Input voltage range	1.8		6	V
V <sub>(VS)</sub>	Output voltage range of the boost converter V <sub>(VS)</sub>			15	V
L	Inductor <sup>(1)</sup>		4.7		μH
T <sub>A</sub>	Operating ambient temperature	-40		125	°C

- (1) See [Typical Application](#) for further information.

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPS65150-Q1	UNIT
		PWP (TSSOP)	
		24 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	40.6	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	20.8	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	18.4	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	0.5	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	18.2	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	1.9	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.5 Electrical Characteristics

 $V_I = 3.3\text{ V}$ ,  $V_{(VS)} = 10\text{ V}$ ,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$ , typical values are at  $T_A = 25^\circ\text{C}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
<b>SUPPLY CURRENT</b>							
$V_I$	Input voltage (VIN)			1.8		6	V
	Supply current (VIN)	Device not switching			14	25	$\mu\text{A}$
	Supply current (SUP)	Device not switching			1.9	3	$\text{mA}$
	Supply current (VCOM buffer)				750	1500	$\mu\text{A}$
$V_{IT-}$	Undervoltage lockout threshold (VIN)	$V_I$ falling	$-40^\circ\text{C} < T_A < 85^\circ\text{C}$		1.6	1.8	V
			$-40^\circ\text{C} < T_A < 125^\circ\text{C}$		1.6	1.85	
$V_{IT+}$	Undervoltage lockout threshold (VIN)	$V_I$ rising	$-40^\circ\text{C} < T_A < 85^\circ\text{C}$		1.7	1.9	V
			$-40^\circ\text{C} < T_A < 125^\circ\text{C}$		1.7	1.95	
	Thermal shutdown temperature threshold	$T_J$ rising			155		$^\circ\text{C}$
	Thermal shutdown temperature hysteresis				10		$^\circ\text{C}$
<b>LOGIC SIGNALS</b>							
$V_{IH}$	High-level input voltage (CTRL)			1.6			V
$V_{IL}$	Low-level input voltage (CTRL)					0.4	V
$I_{IH}$ , $I_{IL}$	Input current (CTRL)	CTRL = $V_I$ or GND			0.01	0.2	$\mu\text{A}$
<b>BOOST CONVERTER</b>							
$V_O$	Output voltage					15	V
$V_{ref}$	Boost converter reference voltage (FB)	$-40^\circ\text{C} < T_A < 85^\circ\text{C}$		1.136	1.146	1.154	V
		$-40^\circ\text{C} < T_A < 125^\circ\text{C}$		1.132	1.146	1.160	
$I_{IB}$	Input bias current (FB)				10	100	$\text{nA}$
$r_{DS(on)}$	Drain-source on-state resistance (Q1)	$I_{DS} = 500\text{ mA}$	$V_O = 10\text{ V}$		200	300	$\text{m}\Omega$
			$V_O = 5\text{ V}$		305	450	
$r_{DS(on)}$	Drain-source on-state resistance (Q2)	$I_{DS} = 500\text{ mA}$	$V_O = 10\text{ V}$		8	15	$\Omega$
			$V_O = 5\text{ V}$		12	22	
$I_{DS}$	Drain-source current rating (Q2)			1			A
	Current limit (Q1)			2	2.5	3.4	A
$I_{(SW)(off)}$	Off-state current (SW)	$V_{(SW)} = 15\text{ V}$			1	10	$\mu\text{A}$
$V_{IT+}$	Overvoltage protection threshold (SUP)	$V_{(SUP)}$ rising		16		20	V
$\Delta V_{O(\Delta VI)}$	Line regulation	$V_I = 1.8\text{ V}$ to $5\text{ V}$	$I_O = 1\text{ mA}$		0.007		%/V
$\Delta V_{O(\Delta IO)}$	Load regulation	$V_I = 5\text{ V}$	$I_O = 0\text{ A}$ to $400\text{ mA}$		0.16		%/A
$V_{IT+}$	Gate drive threshold (FB) <sup>(1)</sup>			$-12\%$ of $V_{ref}$		$-4\%$ of $V_{ref}$	V
<b>NEGATIVE CHARGE PUMP</b>							
$V_O$	Output voltage					-2	V
$V_{(REF)}$	Reference output voltage (REF)	$-40^\circ\text{C} < T_A < 85^\circ\text{C}$		1.205	1.213	1.219	V
		$-40^\circ\text{C} < T_A < 125^\circ\text{C}$		1.203	1.213	1.223	
$V_{ref}$	Feedback regulation voltage (FBN)			-36	0	36	$\text{mV}$
$I_{IB}$	Input bias current (FBN)				10	100	$\text{nA}$
$r_{DS(on)}$	Drain-source on-state resistance (Q4)	$I_{DS} = 20\text{ mA}$			4.4		$\Omega$
$V_{(DRVN)}$	Current sink voltage drop <sup>(2)</sup>	$V_{(FBN)} = 5\%$ above nominal voltage	$I_{(DRVN)} = 50\text{ mA}$		130	300	$\text{mV}$
			$I_{(DRVN)} = 100\text{ mA}$		280	450	
$\Delta V_{O(\Delta IO)}$	Load regulation	$V_O = -5\text{ V}$	$I_O = 0\text{ mA}$ to $20\text{ mA}$		0.016		%/mA

- (1) The GD signal is latched low when the main boost converter output is within regulation. The GD signal is reset when the voltage on the VIN pin goes below the UVLO threshold voltage.
- (2) The maximum charge pump output current is half the drive current of the internal current source or sink.

## Electrical Characteristics (接下页)

 $V_I = 3.3\text{ V}$ ,  $V_{(VS)} = 10\text{ V}$ ,  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$ , typical values are at  $T_A = 25^\circ\text{C}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
<b>POSITIVE CHARGE PUMP</b>							
$V_O$	Output voltage	CTRL = GND	VGH = open			30	V
$V_{ref}$	Feedback regulation voltage (FBP)	CTRL = GND	VGH = open	1.187	1.214	1.238	V
$I_{IB}$	Input bias current (FBP)	CTRL = GND	VGH = open		10	100	nA
$r_{DS(on)}$	Drain-source on-state resistance (Q3)	$I_{DS} = 20\text{ mA}$			1.1		$\Omega$
$V_{(SUP)} - V_{(DRV)}$	Current sink voltage drop <sup>(2)</sup>	$V_{(FBP)} = 5\%$ below nominal voltage	$I_{(DRV)} = 50\text{ mA}$ $I_{(DRV)} = 100\text{ mA}$		420	650	mV
$\Delta V_{O(\Delta IO)}$	Load regulation	$V_O = 24\text{ V}$	$I_O = 0\text{ mA}$ to $20\text{ mA}$		0.07		%/mA
<b>GATE-VOLTAGE SHAPING</b>							
$r_{DS(on)}$	Drain-source on-state resistance (Q5)	$I_O = -20\text{ mA}$			12	30	$\Omega$
$I_{(ADJ)}$	Capacitor charge current	$V_{(ADJ)} = 20\text{ V}$	$V_{(CPI)} = 30\text{ V}$	160	200	240	$\mu\text{A}$
$V_{Omin}$	Minimum output voltage	$V_{(ADJ)} = 0\text{ V}$	$I_O = -10\text{ mA}$		2		V
$I_{OM}$	Maximum output current			20			mA
<b>TIMING CIRCUITS DLY1, DLY2, FDLY</b>							
$I_{(DLY1)}$	Drive current into delay capacitor (DLY1)	$V_{(DLY1)} = 1.213\text{ V}$		3	5	7	$\mu\text{A}$
$I_{(DLY2)}$	Drive current into delay capacitor (DLY2)	$V_{(DLY2)} = 1.213\text{ V}$		3	5	7	$\mu\text{A}$
$R_{(FDLY)}$	Fault time delay resistor			250	450	650	k $\Omega$
<b>GATE DRIVE (GD)</b>							
$V_{(GD\_VS)}$	Gate Drive Threshold	$V_{(VS)}$ rising		-12% of $V_{(SUP)}$		-4% of $V_{(SUP)}$	
$V_{OL}$	Low-level output voltage (GD)	$I_{OL} = 500\text{ }\mu\text{A}$				0.5	V
$I_{OH}$	Off-state current (GD)	$V_{OH} = 15\text{ V}$			0.001	1	$\mu\text{A}$
<b>VCOM BUFFER</b>							
$V_{ISR}$	Single-ended input voltage (IN)			2.25		$V_{(SUP)} - 2\text{ V}$	V
$V_{IO}$	Input offset voltage (IN)	$I_O = 0\text{ mA}$		-25		25	mV
$\Delta V_{O(\Delta IO)}$	Load regulation	$I_O = \pm 25\text{ mA}$		-37		37	mV
		$I_O = \pm 50\text{ mA}$		-77		55	
		$I_O = \pm 100\text{ mA}$		-85		85	
		$I_O = \pm 150\text{ mA}$		-110		110	
$I_{IB}$	Input bias current (IN)			-300	-30	300	nA
$I_{OM}$	Maximum output current (VCOM)	$V_{(SUP)} = 15\text{ V}$			1.2		A
		$V_{(SUP)} = 10\text{ V}$			0.65		
		$V_{(SUP)} = 5\text{ V}$			0.15		

## 6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

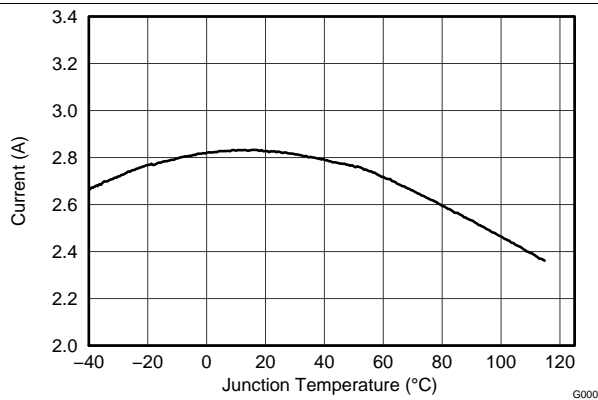
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Oscillator frequency		1.02	1.2	1.38	MHz
Duty cycle (DRVN)			50%		
Duty cycle (DRVN)			50%		

## 6.7 Typical Characteristics

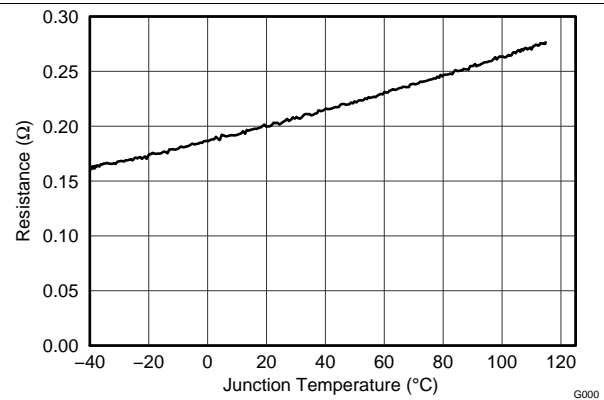
The typical characteristics are measured at 3.3 V

**表 1. Table Of Graphs**

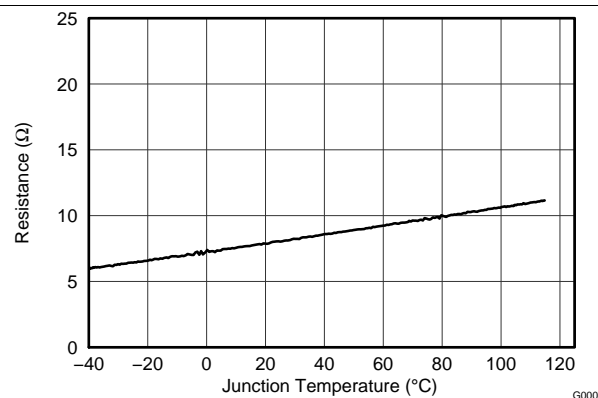
		FIGURE
Boost converter switch (Q1) current limit	vs temperature	<a href="#">图 1</a>
Boost converter switch (Q1) $r_{DS(on)}$	vs temperature	<a href="#">图 2</a>
Boost converter rectifier (Q2) $r_{DS(on)}$	vs temperature	<a href="#">图 3</a>
Boost converter reference Voltage	vs temperature	<a href="#">图 4</a>
Positive charge pump reference voltage	vs temperature	<a href="#">图 5</a>
REF pin voltage	vs temperature	<a href="#">图 6</a>
Oscillator frequency	vs temperature	<a href="#">图 7</a>



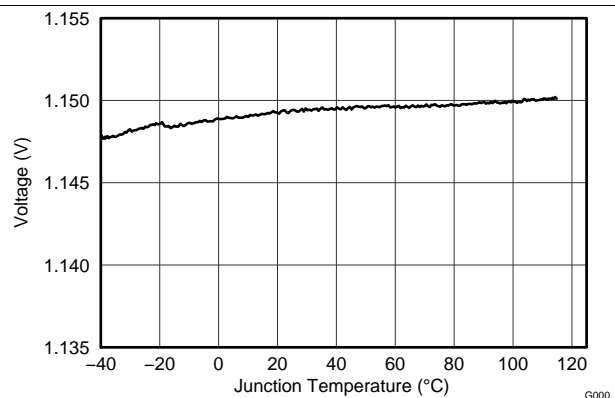
**图 1. Boost Converter Switch (Q1) Current Limit vs Temperature**



**图 2. Boost Converter Switch (Q1)  $r_{DS(on)}$  vs Temperature**



**图 3. Boost Converter Rectifier (Q2)  $r_{DS(on)}$  vs Temperature**



**图 4. Boost Converter Reference Voltage vs Temperature**



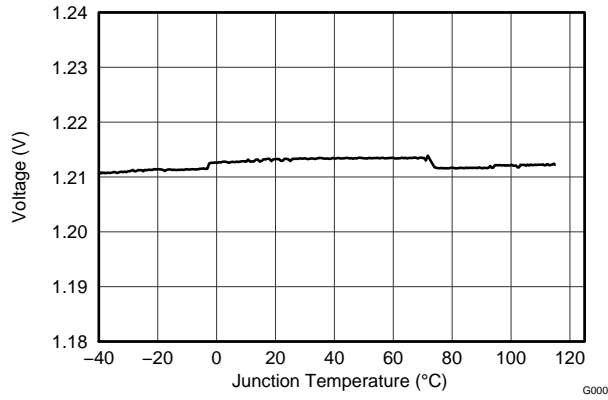


图 5. Positive Charge Pump Reference Voltage vs Temperature

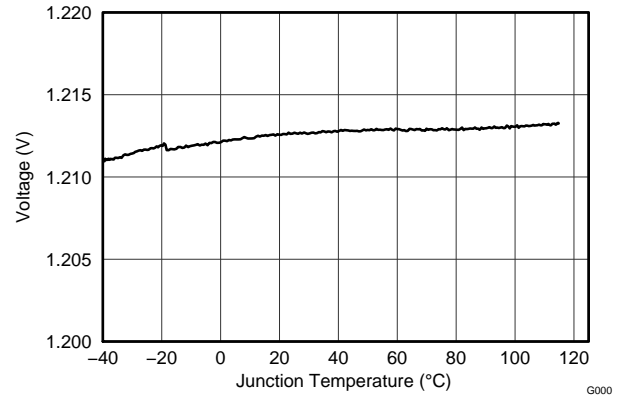


图 6. REF Pin Voltage vs Temperature

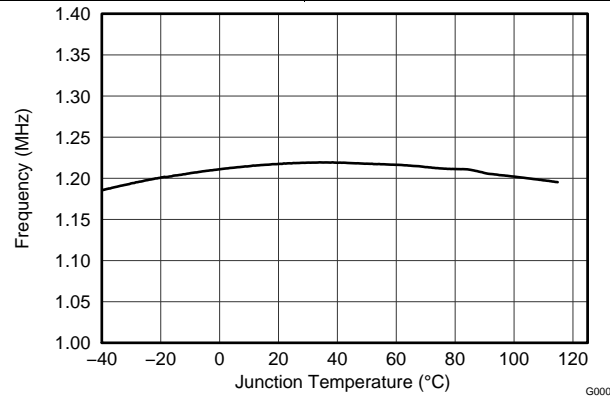


图 7. Oscillator Frequency vs Temperature

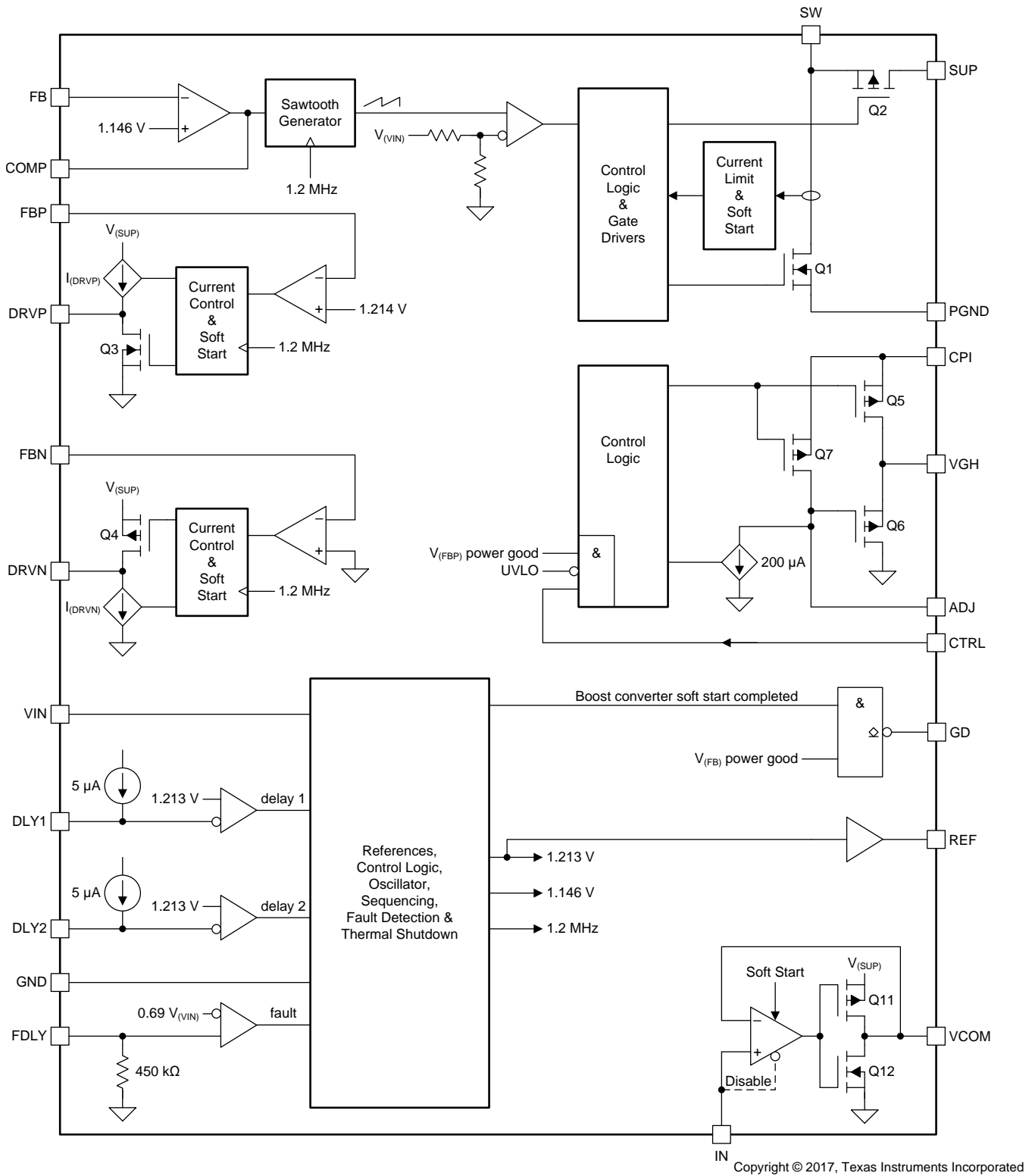
## 7 Detailed Description

### 7.1 Overview

The TPS65150-Q1 device is a complete bias supply for LCD displays. The device generates supply voltages for the source driver and gate driver ICs in the display as well as generating the common plane voltage of the display ( $V_{COM}$ ). The device also features a gate-voltage shaping function that can be used to reduce image sticking and improve picture quality. The use of external components to control power-up sequencing, fault detection time, and boost converter compensation allows the device to be optimized for a variety of displays.

The device has been designed to work from input supply voltages as low as 1.8 V and is therefore ideal for use in applications where it is supplied from fixed 2.5-V, 3.3-V, or 5-V supplies.

## 7.2 Functional Block Diagram

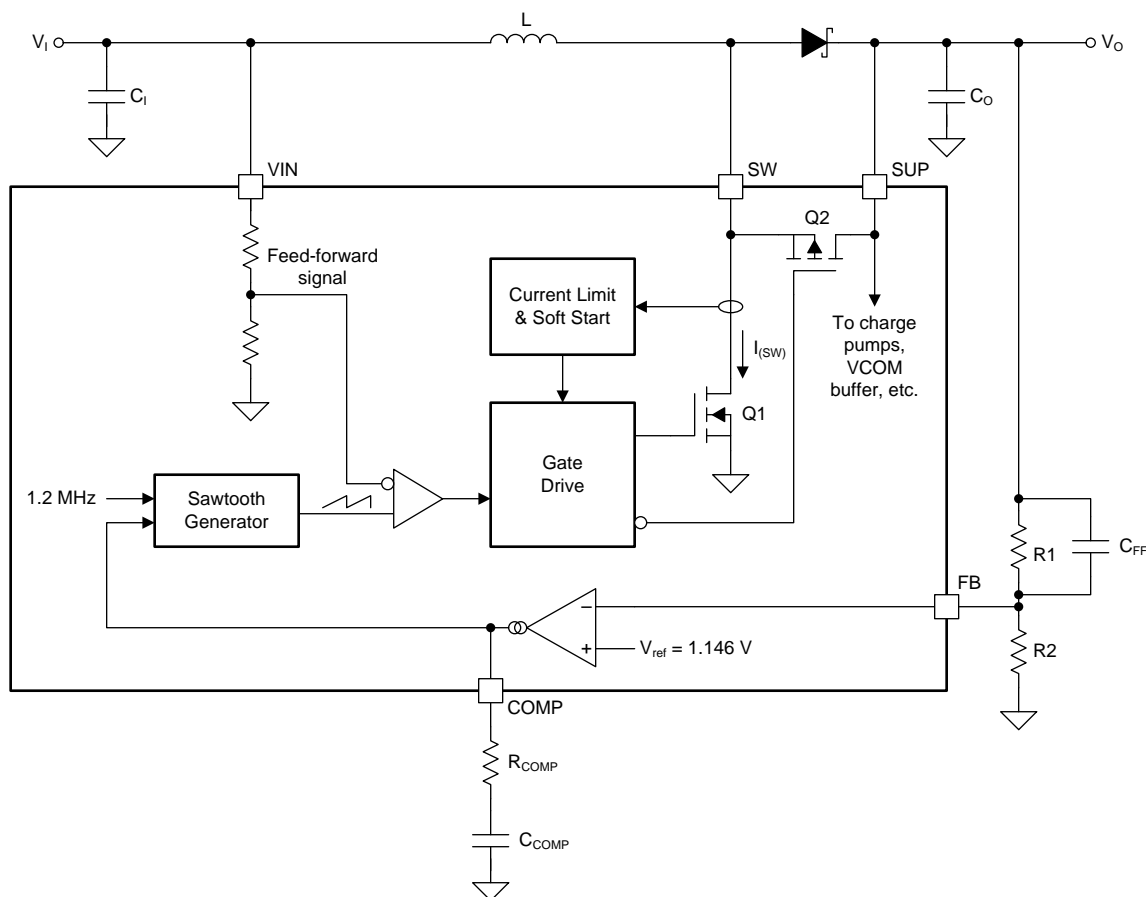


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### 7.3 Feature Description

#### 7.3.1 Boost Converter

图 8 shows a simplified block diagram of the boost converter.



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图 8. Boost Converter Block Diagram

The boost converter uses a unique fast-response voltage-mode controller scheme with input feedforward to achieve excellent line and load regulation, while still allowing the use of small external components. The use of external compensation adds flexibility and allows the response of the boost converter to be optimized for a wide range of external components.

The TPS65150-Q1 device uses a virtual-synchronous topology that allows the boost converter to operate in continuous conduction mode (CCM) even at light loads. This is achieved by including a small MOSFET (Q2) in parallel with the external rectifier diode. Under light-load conditions, Q2 allows the inductor current to become negative, maintaining operation in CCM. By operating always in CCM, boost converter compensation is simplified, ringing on the SW pin at low loads is avoided, and additional charge pump stages can be driven by the SW pin. The boost converter duty cycle is given by 公式 1.

$$D = 1 - \frac{\eta V_I}{V_O}$$

where

- $\eta$  is the boost converter efficiency (either taken from data in [Application Curves](#) or a worst-case assumption of 75%),
- $V_I$  is the boost converter input supply voltage, and
- $V_O$  is the boost converter output voltage.

(1)

## Feature Description (接下页)

Use [公式 2](#) to calculate the boost converter peak switch current.

$$I_{(SW)M} = \frac{DV_I}{2fL} + \frac{I_O}{1-D}$$

where

- $f = 1.2$  MHz (the boost converter switching frequency),
- $I_O$  is the boost converter output current, and
- $L$  is the boost converter inductance.

(2)

### 7.3.1.1 Setting the Boost Converter Output Voltage

The boost converter output voltage is set by the R1/R2 resistor divider, and is calculated using [公式 3](#).

$$V_O = \left(1 + \frac{R1}{R2}\right) V_{ref}$$

where

- $V_{ref} = 1.146$  V (the boost converter internal reference voltage).

(3)

To minimize quiescent current consumption, the value of R1 should be in the range of 100 kΩ to 1 MΩ.

### 7.3.1.2 Boost Converter Rectifier Diode

The reverse voltage rating of the diode must be higher than the maximum output voltage of the converter, and its average forward current rating must be higher than the output current of the boost converter. Use [公式 4](#) to calculate the rectifier diode repetitive peak forward current.

$$I_{FRM} = I_{(SW)M}$$

(4)

Use [公式 5](#) to calculate the power dissipated in the rectifier diode.

$$P_D = V_F I_O$$

where

- $V_F$  is the rectifier diode forward voltage.

(5)

The main diode parameters affecting converter efficiency are its forward voltage and reverse leakage current, and both should be as low as possible.

### 7.3.1.3 Choosing the Boost Converter Output Capacitance

The output capacitance of the boost converter smooths the output voltage and supplies transient output current demands that are outside the loop bandwidth of the converter. Generally speaking, larger output currents or smaller input supply voltages require larger output capacitances. Use [公式 6](#) to calculate the output voltage ripple of the boost converter.

$$V_{O(PP)} = \frac{DI_O}{fC_O}$$

where

- $C_O$  is the boost converter output capacitance.

(6)

### 7.3.1.4 Compensation

The boost converter requires a series R-C network connected between the COMP pin and ground to compensate its feedback loop. The COMP pin is the output of the boost converter's error amplifier, and the compensation capacitor determines the amplifier's low-frequency gain and the resistor its high-frequency gain. Because the converter gain changes with the input voltage, different compensation capacitors may be required: lower input voltages require a higher gain, and therefore a smaller compensation capacitor value. If an input supply voltage of the application changes (for example, if the TPS65150-Q1 device is supplied from a battery), choose compensation components suitable for a supply voltage midway between the minimum and maximum values. In all cases, verify that the values selected are suitable by performing transient tests over the full range of operating conditions.

**Feature Description (接下页)**
**表 2. Recommended Compensation Components for Different Input Supply Voltages**

$V_i$	$C_{COMP}$	$R_{COMP}$	FEED-FORWARD ZERO CUT-OFF FREQUENCY
2.5 V	470 pF	68 k $\Omega$	8.8 kHz
3.3 V	470 pF	33 k $\Omega$	7.8 kHz
5 V	2.2 nF	0 k $\Omega$	11.2 kHz

A feed-forward capacitor  $C_{FF}$  in parallel with the upper feedback resistor R1 adds an additional zero to the loop response, which improves transient performance. 表 2 suggests suitable values for the cut-off frequency of the feedforward zero; however, these are only guidelines. In any application, variations in input supply voltage, inductance, and output capacitance all affect circuit operation, and the optimum value must be verified with transient tests before being finalized.

The cut-off frequency of the feed-forward zero is determined using 公式 7.

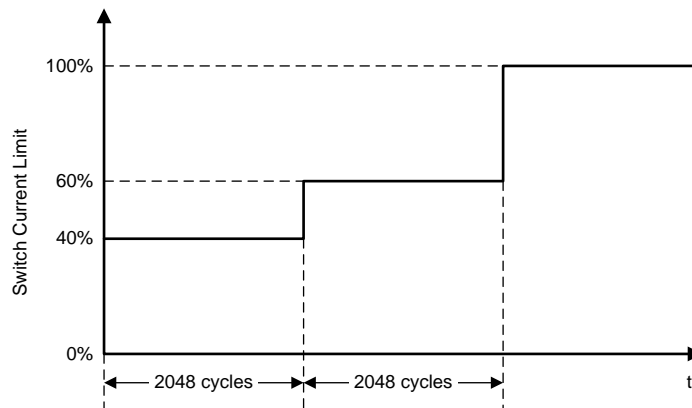
$$f_{co} = \frac{1}{2\pi(R1)C_{FF}}$$

where

- $f_{co}$  is the cutoff frequency of the feedforward zero formed by R1 and  $C_{FF}$ . (7)

**7.3.1.5 Soft Start**

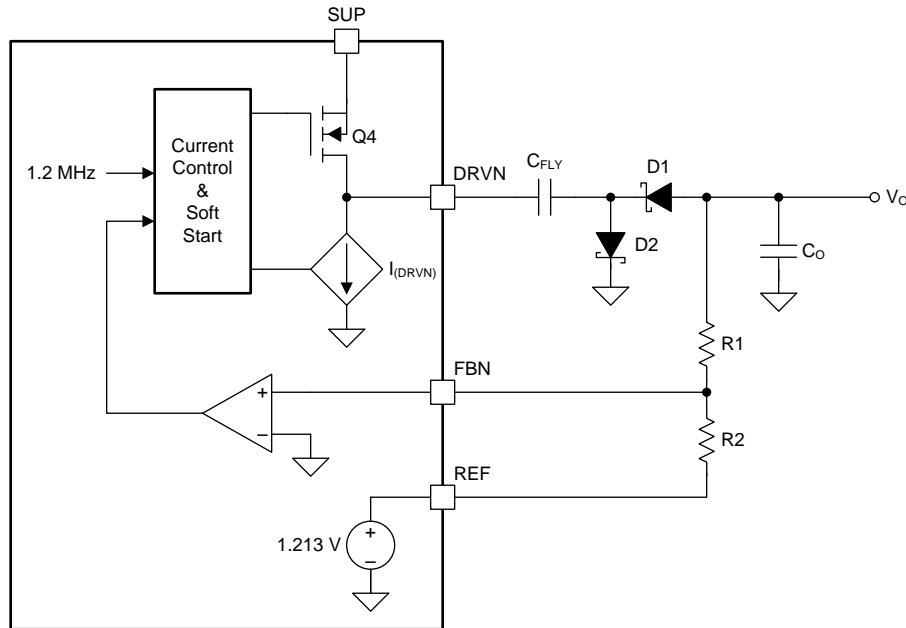
The boost converter features a soft-start function that limits the current drawn from the input supply during start-up. During the first 2048 switching cycles, the switch current of the boost converter is limited to 40% of its maximum value; during the next 2048 cycles, it is limited to 60% of its maximum value; and after that it is as high as it must be to regulate the output voltage (up to 100% of the maximum). In typical applications, this results in a start-up time of about 5 ms (see 图 9).


**图 9. Boost Converter Switch Current Limit During Soft-Start**
**7.3.1.6 Gate Drive Signal**

The GD pin provides a signal to control an external P-channel enhancement MOSFET, allowing the output of the boost converter to be isolated from its input when disabled (see 图 36). The GD pin is an open-drain type whose output is latched low as soon as the output voltage of the boost converter reaches its power-good threshold. The GD pin goes high impedance whenever the input voltage falls below the undervoltage lockout threshold or the device shuts down as the result of a fault condition (see *Adjustable Fault Delay*).

**7.3.2 Negative Charge Pump**

图 10 shows a simplified block diagram of the negative charge pump.



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图 10. Negative Charge Pump Block Diagram

The negative charge pump operates with a fixed frequency of 1.2 MHz and a 50% duty cycle in two distinct phases. During the charge phase, transistor Q4 is turned on, controlled current source  $I_{(DRVN)}$  is turned off, and flying capacitance  $C_{FLY}$  charges up to approximately  $V_{(SUP)}$ . During the discharge phase, Q4 is turned off,  $I_{(DRVN)}$  is turned on, and a negative current of  $I_{(DRVN)}$  flows through D1 to the output. The output voltage is fed back through R1 and R2 to an error amplifier that controls  $I_{(DRVN)}$  so that the output voltage is regulated at the correct value.

### 7.3.2.1 Negative Charge Pump Output Voltage

The negative charge pump output voltage is set by resistors R1 and R2 and is given by 公式 8.

$$V_O = -\left(\frac{R1}{R2}\right)V_{(REF)}$$

where

- $V_{(REF)} = 1.213 \text{ V}$  (the voltage on the REF pin). (8)

Resistor R2 should be in the range 39 kΩ to 150 kΩ. Smaller values load the REF pin too heavily and larger values may cause stability problems.

### 7.3.2.2 Negative Charge Pump Flying Capacitance

The flying capacitance transfers charge from the SUP pin to the negative charge pump output. TI recommends a flying capacitor of at least 100 nF for output currents up to 20 mA. Smaller values can be used with smaller output currents.

### 7.3.2.3 Negative Charge Pump Output Capacitance

The output capacitor smooths the discontinuous current delivered by the flying capacitor to generate a DC output voltage. In general, higher output currents require larger output capacitances. Use 公式 9 to calculate the negative charge pump output voltage ripple.

$$V_{O(PP)} = \frac{I_O}{2fC_O}$$

where

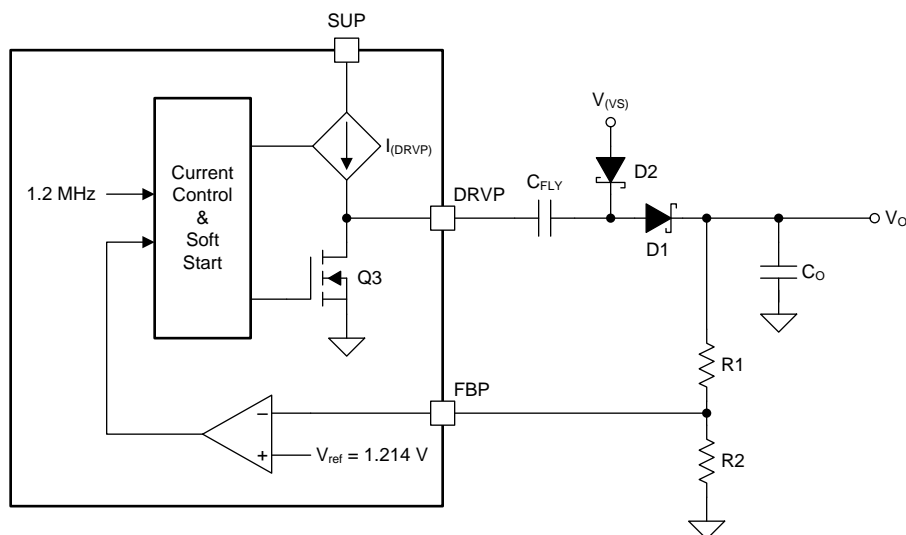
- $I_O$  is the negative charge pump output current,
  - $C_O$  is the negative charge pump output capacitance, and
  - $f = 1.2$  MHz (the negative charge pump switching frequency).
- (9)

### 7.3.2.4 Negative Charge Pump Diodes

The average forward current of both diodes is equal to the negative charge pump output current. If the recommended flying capacitor (or larger) is used, the repetitive peak forward current in D1 and D2 is equal to twice the output current.

### 7.3.3 Positive Charge Pump

图 11 shows a simplified block diagram of the positive charge pump, which works in a similar way to the negative charge pump except that the positions of the current source  $I_{DRVP}$  and the MOSFET Q3 are reversed.



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图 11. Positive Charge Pump Block Diagram

If higher output voltages are required another charge pump stage can be added to the output, as shown in 图 34 at the end of the data sheet.

#### 7.3.3.1 Positive Charge Pump Output Voltage

The positive charge pump output voltage is set by resistors R1 and R2 and is calculated using 公式 10.

$$V_O = \left(1 + \frac{R1}{R2}\right) V_{ref}$$

where

- $V_{ref} = 1.214$  V (the positive charge pump reference voltage).
- (10)

TI recommends choosing a value for R2 not greater than 1 MΩ.

#### 7.3.3.2 Positive Charge Pump Flying Capacitance

The flying capacitance transfers charge from the SUP pin to the charge pump output. TI recommends a flying capacitor of at least 330 nF <sup>(1)</sup> for output currents up to 20 mA. Smaller values can be used with smaller output currents.

(1) The minimum recommended flying capacitance for the positive charge pump is larger than for the negative charge pump because the  $r_{DS(on)}$  of Q3 is smaller than the  $r_{DS(on)}$  of Q4.



### 7.3.3.3 Positive Charge Pump Output Capacitance

The output voltage ripple of the positive charge pump is given by 公式 11.

$$V_{O(PP)} = \frac{I_o}{2fC_o}$$

where

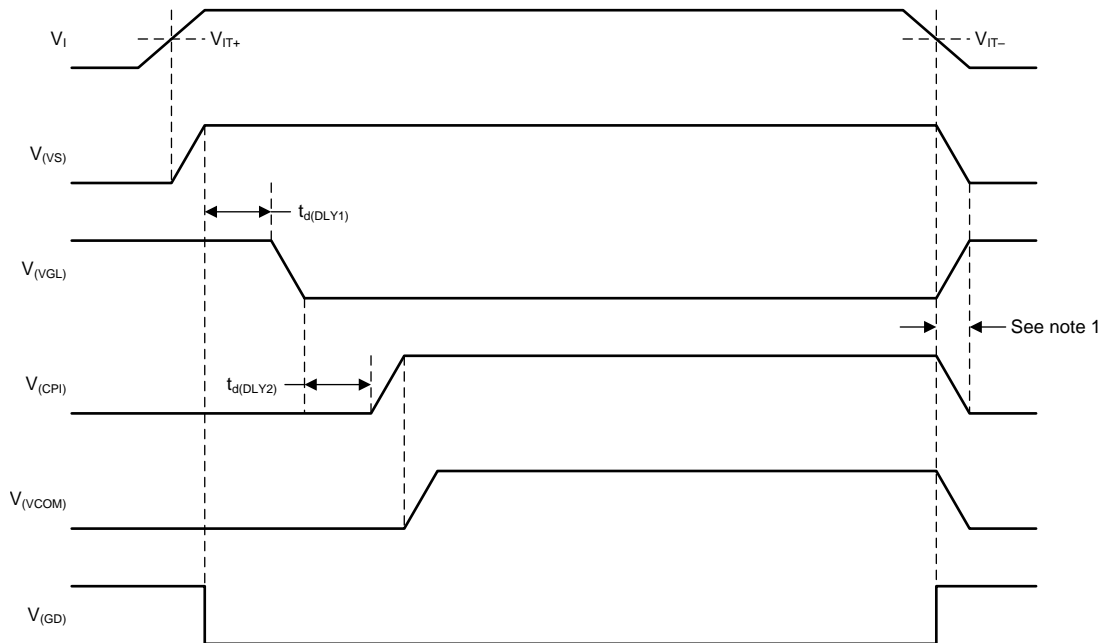
- $I_o$  is the output current of the positive charge pump,
  - $C_o$  is the output capacitance of the positive charge pump, and
  - $f = 1.2$  MHz (the switching frequency of the positive charge pump).
- (11)

### 7.3.3.4 Positive Charge Pump Diodes

The average forward current of both diodes is equal to the positive charge pump output current. If the recommended flying capacitance (or larger) is used, the repetitive peak forward current in D1 and D2 equal to twice the output current.

### 7.3.4 Power-On Sequencing, DLY1, DLY2

The boost converter starts as soon as the input supply voltage exceeds the rising UVLO threshold. The negative charge pump starts  $t_{d(DLY1)}$  seconds after the boost converter output voltage has reached its final value, and the positive charge pump starts  $t_{d(DLY2)}$  seconds after the output of the negative charge pump has reached its final value. The VCOM buffer starts up as soon as the output voltage of the positive charge pump ( $V_{(CPI)}$ ) has reached its final value.



**Notes**

1. The fall times of  $V_{(VS)}$ ,  $V_{(VGL)}$ ,  $V_{(CPI)}$  depend on their respective load currents and feedback resistances.

**图 12. Start-Up Sequencing With CTRL = High**

The delay times  $t_{d(DLY1)}$  and  $t_{d(DLY2)}$  are set by the capacitors connected to the DLY1 and DLY2 pins respectively. Each of these pins is connected to its own 5- $\mu$ A current source ( $I_{(DLY1)}$  and  $I_{(DLY2)}$ ) that causes the voltage on the external capacitor to ramp up linearly. The delay time is defined by how long it takes the voltage on the external capacitor to reach the reference voltage, and is given by 公式 12.

$$t_{d(DLY1)} = \frac{C_{DLY1} V_{ref}}{I_{(DLY1)}} \quad \text{and} \quad t_{d(DLY2)} = \frac{C_{DLY2} V_{ref}}{I_{(DLY2)}}$$

where

- $V_{ref} = 1.213 \text{ V}$  (the internal reference voltage),
  - $I_{(DLY1)} = 5 \mu\text{A}$  (the DLY1 pin output current), and
  - $I_{(DLY2)} = 5 \mu\text{A}$  (the DLY2 pin output current).
- (12)

### 7.3.5 Gate Voltage Shaping

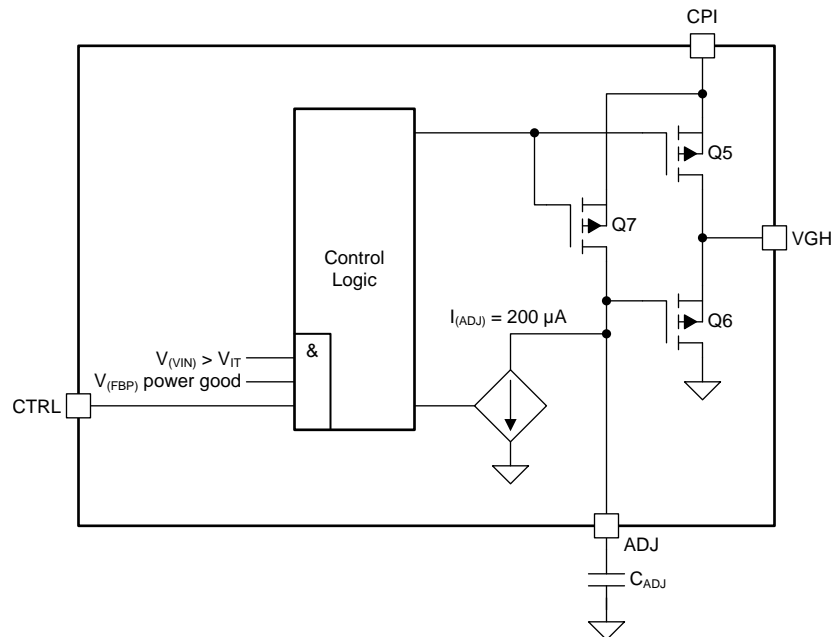
The gate voltage shaping function can be used to reduce crosstalk between LCD pixels by reducing the gate drivers' input supply voltage between lines. 图 13 shows a simplified block diagram of the gate voltage shaping function. Gate voltage shaping is controlled by a logic-level signal applied to the CTRL pin. When CTRL is high, Q5 and Q7 are on and Q6 is off, and the output of the positive charge pump is connected to the VGH pin. When CTRL is low, Q5 and Q7 are off and Q6 is on. Q6 operates as a source follower and tracks the voltage on the ADJ pin, which ramps down linearly as the current sink  $I_{(ADJ)}$  discharges the external capacitor  $C_{ADJ}$  (see 图 14). The peak-to-peak voltage on the VGH pin is determined by the value of  $C_{ADJ}$  and the duration of the low level applied to the CTRL pin, and is calculated using 公式 13.

$$V_{(VGH)(PP)} = \frac{I_{(ADJ)} t_{w(CTRL)}}{C_{ADJ}}$$

where

- $I_{(ADJ)} = 200 \mu\text{A}$  (ADJ pin output current),
  - $t_{w(CTRL)}$  is the duration of the low-level signal connected to the CTRL pin, and
  - $C_{ADJ}$  is the capacitance connected to the ADJ pin.
- (13)

When the input supply voltage is below the UVLO threshold or the device enters a shutdown condition because of a fault on one or more of its outputs, Q5 and Q6 turn off and the VGH pin is high impedance.



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图 13. Gate Voltage Shaping Block Diagram

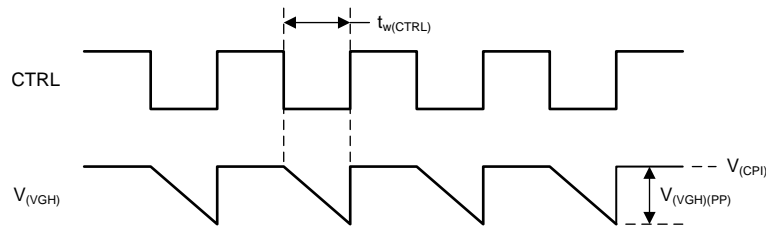


图 14. Gate Voltage Shaping Timing

### 7.3.6 VCOM Buffer

The VCOM Buffer is a transconductance amplifier designed to drive capacitive loads. The IN pin is the input of the VCOM buffer. The VCOM buffer features a soft-start function that reduces the current drawn from the SUP pin when the amplifier starts up.

If the VCOM buffer is not required for certain applications, it is possible to shut down the VCOM buffer by connecting IN to ground, reducing the overall quiescent current. The IN pin cannot be pulled dynamically to ground during operation.

### 7.3.7 Protection

#### 7.3.7.1 Boost Converter Overvoltage Protection

The boost converter features an overvoltage protection function that monitors the voltage on the SUP pin and forces the TPS65150-Q1 device to enter fault mode if the boost converter output voltage exceeds the overvoltage threshold.

#### 7.3.7.2 Adjustable Fault Delay

The TPS65150-Q1 device detects a fault condition and shuts down if the boost converter output or either of the charge pump outputs falls out of regulation for longer than the fault delay time  $t_{d(FDLY)}$ . Fault conditions are detected by comparing the voltage on the feedback pins with the internal power-good thresholds. Outputs that fall below their power-good threshold but recover within less than  $t_{d(FDLY)}$  seconds are not detected as faults and the device does not shut down in such cases. The output fault detection function is active during start-up, so the device shuts down if any of its outputs fails to reach its power-good threshold during start-up. Shut-down following an output voltage fault is a latched condition, and the input supply voltage must be cycled to recover normal operation after it occurs.

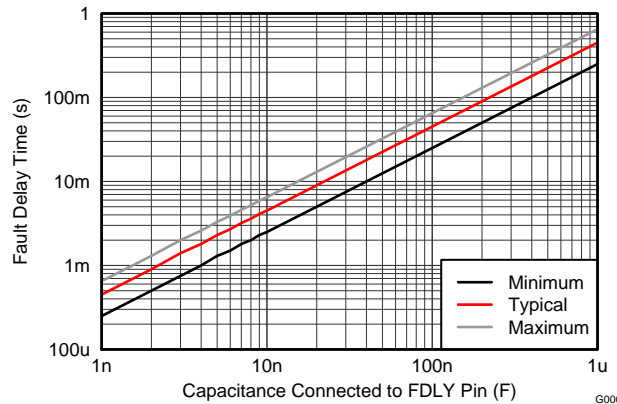
The fault detection delay time is set by the capacitor connected between the FDLY and VIN pins and is given by [公式 14](#).

$$t_{d(FDLY)} = R_{(FDLY)} C_{FDLY}$$

where

- $R_{(FDLY)}$  = 450 k $\Omega$  (the internal resistance connected to the FDLY pin) and
- $C_{FDLY}$  is the external capacitance connected to the FDLY pin.

(14)



**图 15. Adjustable Fault Delay Time**

### 7.3.7.3 Thermal Shutdown

A thermal shutdown is implemented to prevent damage because of excessive heat and power dissipation. Typically, the thermal shutdown threshold is 155°C. When this threshold is reached, the device enters shutdown. The device can be enabled again by cycling the input supply voltage.

### 7.3.7.4 Undervoltage Lockout

The TPS65150-Q1 device has an undervoltage lockout (UVLO) function. The UVLO function stops device operation if the voltage on the VIN pin is less than the UVLO threshold voltage. This makes sure that the device only operates when the supply voltage is high enough for correct operation.

## 7.4 Device Functional Modes

图 16 shows the functional modes of the TPS65150-Q1.

### 7.4.1 $V_I > V_{IT+}$

When the input supply voltage is above the undervoltage lockout threshold, the device is on and all its functions are enabled. Note that full performance may not be available until the input supply voltage exceeds the minimum value specified in [Recommended Operating Conditions](#).

### 7.4.2 $V_I < V_{IT-}$

When the input supply voltage is below the undervoltage lockout threshold, the TPS65150-Q1 device is off and all its functions are disabled.

### 7.4.3 Fault Mode

The TPS65150-Q1 device immediately enters fault mode when any of the following is detected:

- boost converter overvoltage
- overtemperature

The TPS65150-Q1 device also enters fault mode if any of the following conditions is detected and persists for longer than  $t_{d(FDLY)}$ :

- boost converter output out of regulation
- negative charge pump output out of regulation
- positive charge pump output out of regulation

The TPS65150-Q1 device does not function during fault mode. Cycle the input supply voltage to exit fault mode and recover normal operation.

Device Functional Modes (接下页)

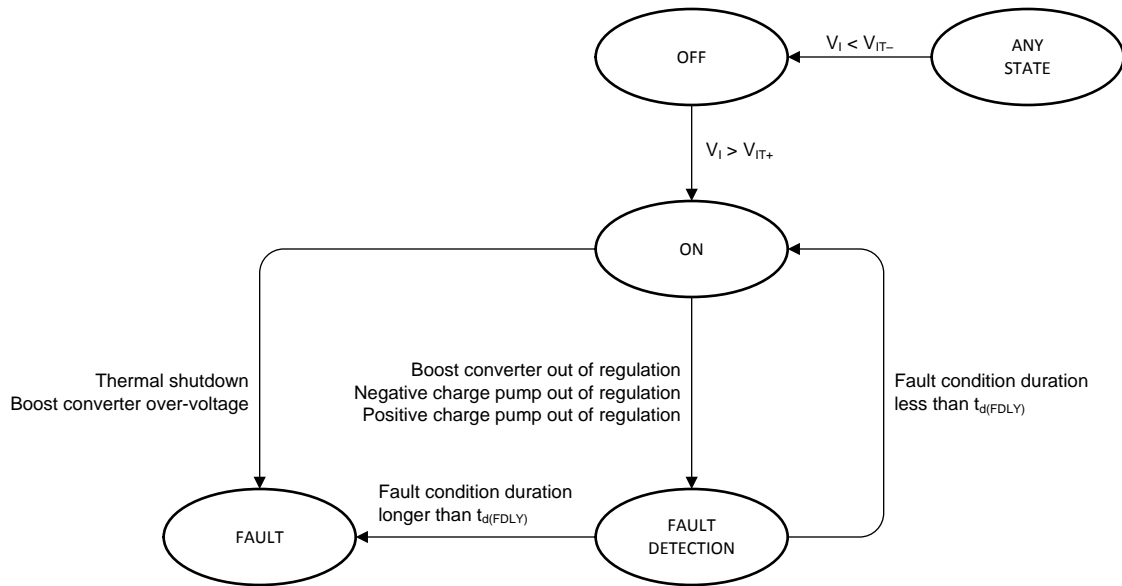


图 16. Functional Modes

## 8 Application and Implementation

### 注

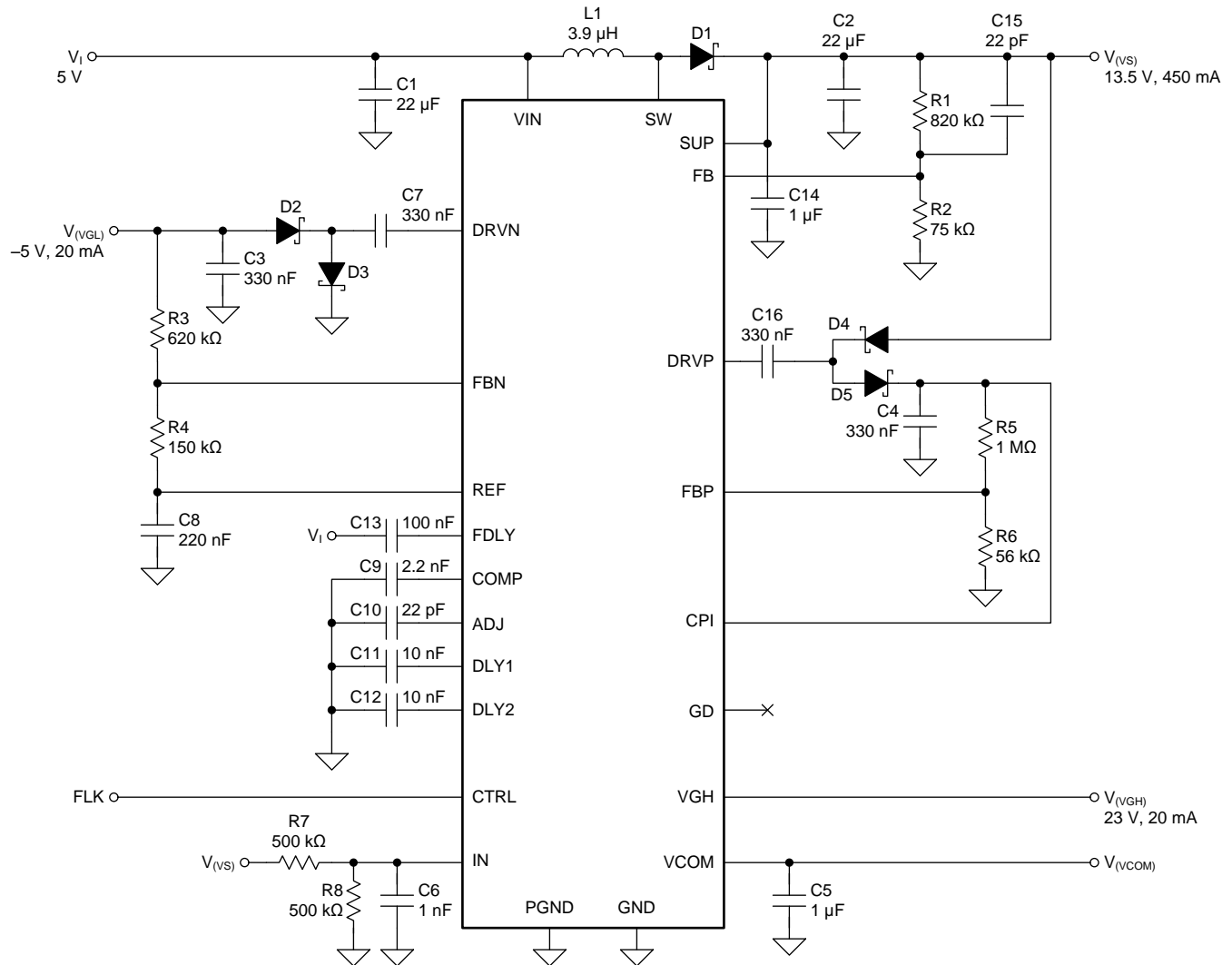
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The TPS65150-Q1 device has been designed to provide the input supply voltages for the source drivers and gate drivers plus the voltage for the common plane in LCD display applications. In addition, the device provides a gate voltage shaping function that can be used to modulate the gate drivers' positive supply to reduce image sticking.

### 8.2 Typical Application

图 17 shows a typical application circuit for a monitor display powered from a 5-V supply. It generates up to 450 mA at 13.5 V to power the source drivers, and 20 mA at 23 V and -5 V to power the gate drivers.



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图 17. Monitor LCD Supply Powered from a 5-V Rail

## Typical Application (接下页)

### 8.2.1 Design Requirements

表 3 shows the parameters for this example.

**表 3. Design Parameters**

PARAMETER		VALUE
$V_I$	Input supply voltage	5 V
$V_{(VS)}$	Boost converter output voltage and current	13.5 V at 450 mA
$V_{(VS)(PP)}$	Boost converter peak-to-peak output voltage ripple	10 mV
$V_{(CPI)}$	Positive charge pump output voltage and current	23 V at 20 mA
$V_{(VGH)(PP)}$	Positive charge pump peak-to-peak output voltage ripple	100 mV
$V_{(VGL)}$	Negative charge pump output voltage and current	-5 V at 20 mA
$V_{(VGL)(PP)}$	Negative charge pump peak-to-peak output voltage ripple	100 mV
$t_{d1}$	Negative charge pump start-up delay time	1 ms
$t_{d2}$	Positive charge pump start-up delay time	1 ms
$t_{d(fault)}$	Fault delay time	45 ms
	Gate voltage shaping slope	10 V/ $\mu$ s

### 8.2.2 Detailed Design Procedure

#### 8.2.2.1 Boost Converter Design Procedure

##### 8.2.2.1.1 Inductor Selection

Several inductors work with the TPS65150-Q1, and with external compensation the performance can be adjusted to the specific application requirements.

The main parameter for the inductor selection is the inductor saturation current, which must be higher than the peak switch current as calculated in 公式 2 with additional margin to cover for heavy load transients. The alternative, more conservative approach, is to choose the inductor with a saturation current at least as high as the maximum switch current limit of 3.4 A.

The second important parameter is the inductor DC resistance. Usually, the lower the DC resistance the higher the efficiency. It is important to note that the inductor DC resistance is not the only parameter determining the efficiency. For a boost converter, where the inductor is the energy storage element, the type and material of the inductor influences the efficiency as well. Especially at a switching frequency of 1.2 MHz, inductor core losses, proximity effects, and skin effects become more important. Usually, an inductor with a larger form factor gives higher efficiency. The efficiency difference between different inductors can vary from 2% to 10%. For the TPS65150-Q1, inductor values from 3.3  $\mu$ H and 6.8  $\mu$ H are a good choice, but other values can be used as well. Possible inductors are shown in 表 4. Equivalent parts can also be used.

**表 4. Inductor Selection<sup>(1)</sup>**

INDUCTANCE	$I_{SAT}$	DCR	MANUFACTURER	PART NUMBER	DIMENSIONS
4.7 $\mu$ H	2.6 A	54 m $\Omega$	Coilcraft	DO1813P-472HC	8.89 mm $\times$ 6.1 mm $\times$ 5 mm
4.2 $\mu$ H	2.2 A	23 m $\Omega$	Sumida	CDRH5D28-4R2	5.7 mm $\times$ 5.7 mm $\times$ 3 mm
4.7 $\mu$ H	1.6 A	48 m $\Omega$	Sumida	CDC5D23-4R7	6 mm $\times$ 6 mm $\times$ 2.5 mm
4.2 $\mu$ H	1.8 A	60 m $\Omega$	Sumida	CDRH6D12-4R2	6.5 mm $\times$ 6.5 mm $\times$ 1.5 mm
3.9 $\mu$ H	2.6 A	20 m $\Omega$	Sumida	CDRH6D28-3R9	7 mm $\times$ 7 mm $\times$ 3 mm
3.3 $\mu$ H	1.9 A	50 m $\Omega$	Sumida	CDRH6D12-3R3	6.5 mm $\times$ 6.5 mm $\times$ 1.5 mm

(1) See [Third-party Products](#) disclaimer

The first step in the design procedure is to verify whether the maximum possible output current of the boost converter supports the specific application requirements. A simple approach is to estimate the converter efficiency, by taking the efficiency numbers from the provided efficiency curves, or use a worst case assumption for the expected efficiency, for example, 75%.

From [图 19](#), it can be seen that the boost converter efficiency is about 85% when operating under the target application conditions. Inserting these values into [公式 1](#) yields [公式 15](#).

$$D = 1 - \frac{(0.85)(5 \text{ V})}{13.5 \text{ V}} = 0.69 \quad (15)$$

and from [公式 2](#), the peak switch current can be calculated as [公式 16](#).

$$I_{(SW)M} = \frac{(0.69)(5 \text{ V})}{2(1.2 \text{ MHz})(3.9 \mu\text{H})} + \frac{(0.45 \text{ A})}{1 - 0.69} = 1.8 \text{ A} \quad (16)$$

The peak switch current is the peak current that the integrated switch, inductor, and rectifier diode must be able to handle. The calculation must be done for the minimum input voltage where the peak switch current is highest. For the calculation of the maximum current delivered by the boost converter, it must be considered that the positive and negative charge pumps as well as the VCOM buffer run from the output of the boost converter as well.

### 8.2.2.2 Rectifier Diode Selection

The rectifier diode reverse voltage rating must be higher than the maximum output voltage of the converter (13.5 V in this application); its average forward current rating must be higher than the maximum boost converter output current of 450 mA, and its repetitive peak forward current must be greater than or equal to the peak switch current of 1.8 A. Not all diode manufacturers specify repetitive peak forward current; however, a diode with an average forward current rating of 1 A or higher is suitable for most practical applications.

From [公式 5](#), the power dissipated in the rectifier diode is calculated with [公式 17](#).

$$P_D = I_O V_F = (0.45 \text{ A})(0.5 \text{ V}) = 0.225 \text{ W} \quad (17)$$

[表 5](#) lists a number of suitable rectifier diodes, any of which would be suitable for this application. Equivalent parts can also be used.

**表 5. Rectifier Diode Selection<sup>(1)</sup>**

$I_{F(AV)}$	$V_R$	$V_F$	MANUFACTURER	PART NUMBER
2 A	20 V	0.44 V at 2 A	Vishay Semiconductor	SL22
2 A	20 V	0.5 V at 2 A	Fairchild Semiconductor	SS22
1 A	30 V	0.44 V at 2 A	Fairchild Semiconductor	MBRS130L
1 A	20 V	0.45 V at 1 A	Microsemi	UPS120
1 A	20 V	0.45 V at 1 A	ON Semiconductor	MBRM120

(1) See [Third-party Products](#) disclaimer.

### 8.2.2.3 Setting the Output Voltage

Rearranging [公式 3](#) and inserting the application parameters yields [公式 18](#).

$$\frac{R1}{R2} = \frac{13.5 \text{ V}}{1.146 \text{ V}} - 1 = 10.78 \quad (18)$$

Standard values of  $R1 = 820 \text{ k}\Omega$  and  $R2 = 75 \text{ k}\Omega$  result in a nominal output voltage of 13.68 V and satisfy the recommendation that the value  $R1$  be lower than 1 M $\Omega$ .

### 8.2.2.4 Output Capacitor Selection

For best output voltage filtering, a low ESR output capacitor is recommended. Ceramic capacitors have a low ESR value, but tantalum capacitors can be used as well, depending on the application. A 22- $\mu\text{F}$  ceramic output capacitor works for most applications. Higher capacitor values can be used to improve the load transient regulation. See [表 6](#) for the selection of the output capacitor.



Rearranging 公式 6 and inserting the application parameters, the minimum value of output capacitance is given by 公式 19.

$$C_o = \frac{1 - 0.69}{(1.2 \text{ MHz})(10 \text{ mV})} \left( 1.8 \text{ A} - 0.45 \text{ A} - \left( \frac{13.5 \text{ V} - 5 \text{ V}}{3.9 \mu\text{H}} \right) \left( \frac{1 - 0.69}{1.2 \text{ MHz}} \right) \right) = 20.3 \mu\text{F} \quad (19)$$

The closest standard value is 22  $\mu\text{F}$ . In practice, TI recommends connecting an additional 1- $\mu\text{F}$  capacitor directly to the SUP pin to ensure a clean supply to the internal circuitry that runs from this supply voltage.

### 8.2.2.5 Input Capacitor Selection

For good input voltage filtering, low ESR ceramic capacitors are recommended. A 22- $\mu\text{F}$  ceramic input capacitor is sufficient for most applications. For better input voltage filtering, this value can be increased. See 表 6 for input capacitor recommendations. Equivalent parts can also be used.

**表 6. Input and Output Capacitance Selection**

CAPACITANCE	VOLTAGE RATING	MANUFACTURER	PART NUMBER	SIZE
22 $\mu\text{F}$	16 V	Taiyo Yuden	EMK325BY226MM	1206
22 $\mu\text{F}$	6.3 V	Taiyo Yuden	JMK316BJ226	1206

### 8.2.2.6 Compensation

From 表 2, it can be seen that the recommended values for C9 and R9 when  $V_I = 5 \text{ V}$  are 2.2 nF and 0  $\Omega$  respectively, and that a feedforward zero at 11.2 kHz must be added.

Rearranging 公式 7 yields 公式 20.

$$C15 = \frac{1}{2\pi f_{co}(R1)} \quad (20)$$

Inserting  $f_{co} = 11.2 \text{ kHz}$  and  $R1 = 820 \text{ k}\Omega$  yields .

$$C15 = \frac{1}{2\pi(11.2 \text{ kHz})(820 \text{ k}\Omega)} = 17 \text{ pF}$$

In this case, a standard value of 22 pF was used.

### 8.2.2.7 Negative Charge Pump

#### 8.2.2.7.1 Choosing the Output Capacitance

Rearranging 公式 9 and inserting the application parameters, the minimum recommended value of C3 is given by 公式 21.

$$C3 = \frac{I_o}{2fV_{O(PP)}} = \frac{20 \text{ mA}}{2(1.2 \text{ MHz})(100 \text{ mV})} = 83 \text{ nF} \quad (21)$$

In this application, a capacitor of 330 nF was used to allow the same value to be used for all charge pump capacitors.

#### 8.2.2.7.2 Choosing the Flying Capacitance

A minimum flying capacitance of 100 nF is recommended. In this application, a capacitor of 330 nF was used to allow the same value to be used for all charge pump capacitors.

#### 8.2.2.7.3 Choosing the Feedback Resistors

The ratio of R3 to R4 required to generate an output voltage of  $-5 \text{ V}$  is given by 公式 22.

$$R3 = -\left( \frac{V_o}{V_{(REF)}} \right) R4 = -\left( \frac{-5 \text{ V}}{1.213 \text{ V}} \right) R4 = (4.122)R4 \quad (22)$$

Values of  $R3 = 620 \text{ k}\Omega$  and  $R4 = 150 \text{ k}\Omega$  generate a nominal output voltage of  $-5.014 \text{ V}$  and load the REF pin with only 8  $\mu\text{A}$ .

#### 8.2.2.7.4 Choosing the Diodes

The average forward current in D2 and D3 is equal to the output current and therefore a maximum of 20 mA. The peak repetitive forward current in D2 and D3 is equal to twice the output current and therefore less than 40 mA.

The BAT54S comprises two Schottky diodes in a small SOT-23 package and easily meets the current requirements of this application.

#### 8.2.2.8 Positive Charge Pump

##### 8.2.2.8.1 Choosing the Flying Capacitance

A minimum flying capacitor of 330 nF is recommended.

##### 8.2.2.8.2 Choosing the Output Capacitance

Rearranging 公式 10 and inserting the application parameters yields 公式 23.

$$C4 = \frac{(20 \text{ mA})}{2(1.2 \text{ MHz})(100 \text{ mV})} = 83 \text{ nF} \quad (23)$$

In this application, a nominal value of 330 nF was used to allow the same value to be used for all charge pump capacitors.

##### 8.2.2.8.3 Choosing the Feedback Resistors

Rearranging 公式 8 and inserting the application parameters yields 公式 24.

$$\frac{R5}{R6} = \frac{23 \text{ V}}{1.214 \text{ V}} - 1 = 17.95 \quad (24)$$

Standard values of 1 MΩ and 56 kΩ result in a nominal output voltage of 22.89 V.

##### 8.2.2.8.4 Choosing the Diodes

The average forward current in D4 and D5 is equal to the output current and therefore a maximum of 20 mA. The peak repetitive forward current in D4 and D5 is equal to twice the output current and therefore less than 40 mA.

#### 8.2.2.9 Gate Voltage Shaping

Rearranging 公式 13 and inserting  $I_{(ADJ)} = 200 \mu\text{A}$  and slope = 10 V/μs yields 公式 25.

$$C10 = \frac{I_{(ADJ)}}{\text{slope}} = \frac{200 \mu\text{A}}{10 \text{ V}/\mu\text{s}} = 20 \text{ pF} \quad (25)$$

The closest standard value for C10 is 22 pF.

#### 8.2.2.10 Power-On Sequencing

Rearranging 公式 12 and inserting  $t_{d1} = t_{d2} = 1 \text{ ms}$  and  $V_{ref2} = 1.213 \text{ V}$ , yields 公式 26.

$$C11 = C12 = \frac{(5 \mu\text{A})(2.5 \text{ ms})}{1.213 \text{ V}} = 10.31 \text{ nF} \quad (26)$$

10 nF is the closest standard value.

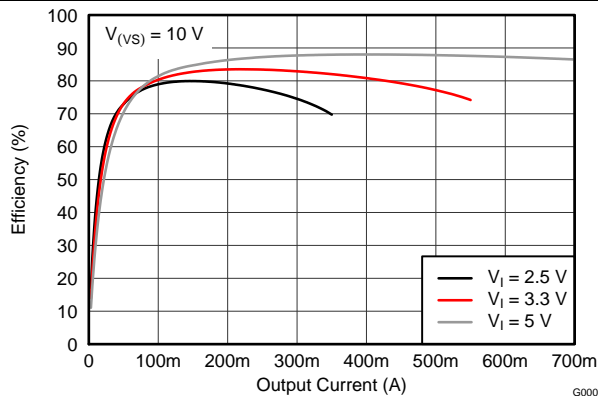
#### 8.2.2.11 Fault Delay

Rearranging 公式 14 and inserting  $t_{d(FDLY)} = 45 \text{ ms}$  yields 公式 27.

$$C_{FDLY} = \frac{45 \text{ ms}}{450 \text{ k}\Omega} = 100 \text{ nF} \quad (27)$$

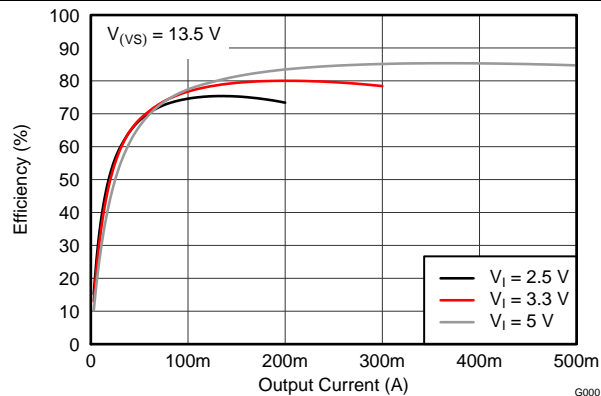
100 nF is a standard value.

8.2.3 Application Curves



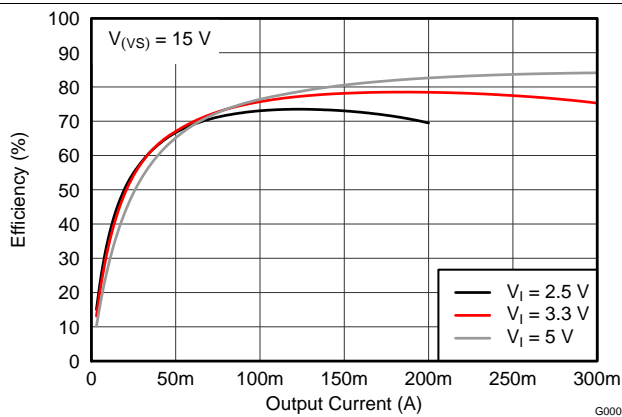
$I_{(VGH)} = 0 \text{ mA}$   $I_{(VGL)} = 0 \text{ mA}$

图 18. Boost Converter Efficiency ( $V_{(VS)} = 10 \text{ V}$ ,  $I_{(VGH)} = I_{(VGL)} = 0 \text{ mA}$ )



$I_{(VGH)} = 0 \text{ mA}$   $I_{(VGL)} = 0 \text{ mA}$

图 19. Boost Converter Efficiency ( $V_{(VS)} = 13.5 \text{ V}$ ,  $I_{(VGH)} = I_{(VGL)} = 0 \text{ mA}$ )



$I_{(VGH)} = 0 \text{ mA}$   $I_{(VGL)} = 0 \text{ mA}$

图 20. Boost Converter Efficiency ( $V_{(VS)} = 15 \text{ V}$ ,  $I_{(VGH)} = I_{(VGL)} = 0 \text{ mA}$ )

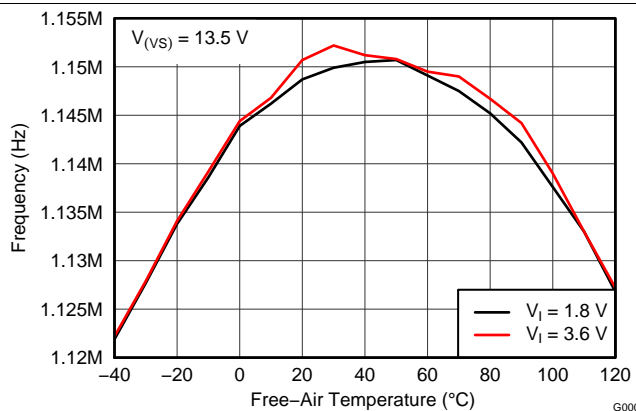


图 21. Boost Converter Switching Frequency

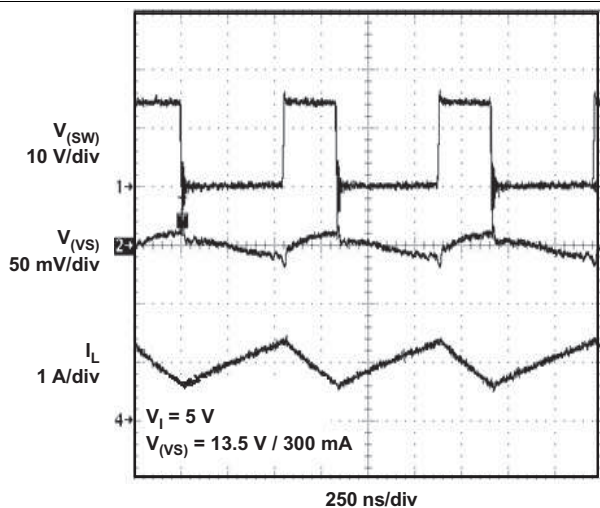


图 22. Boost Converter Operation (Nominal Load)

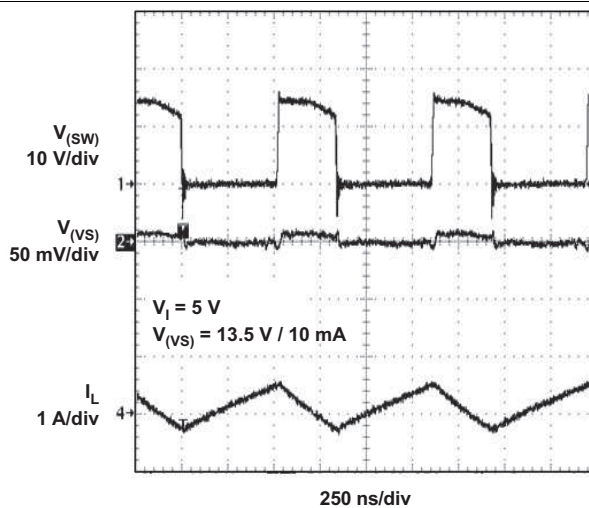


图 23. Boost Converter Operation (Light Load)

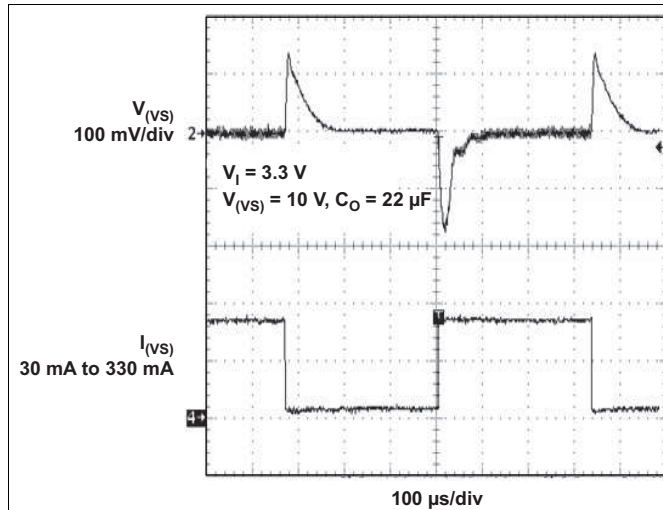


图 24. Boost Converter Load Transient Response

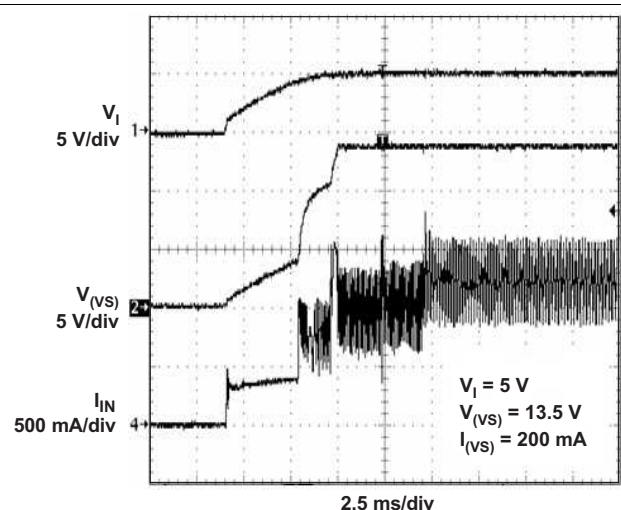


图 25. Boost Converter Soft Start

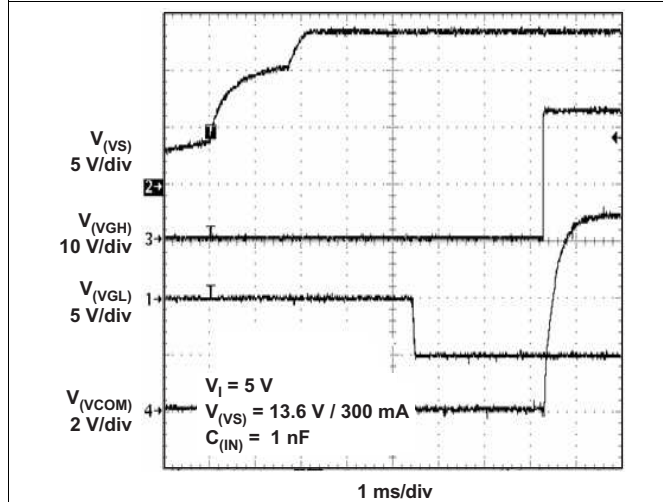


图 26. Power-On Sequencing

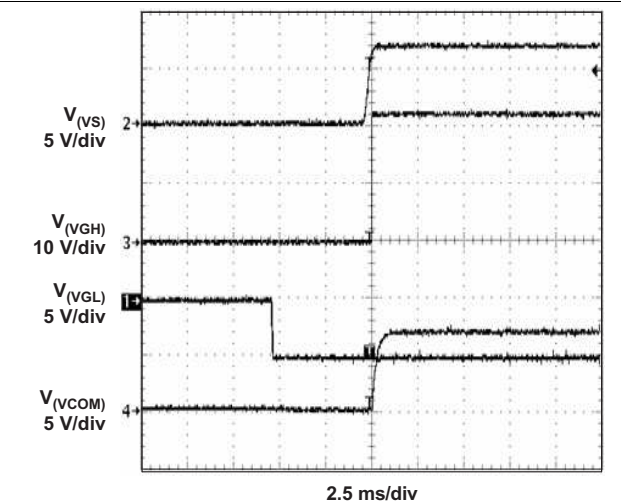


图 27. Power-On Sequencing With External Isolation MOSFET

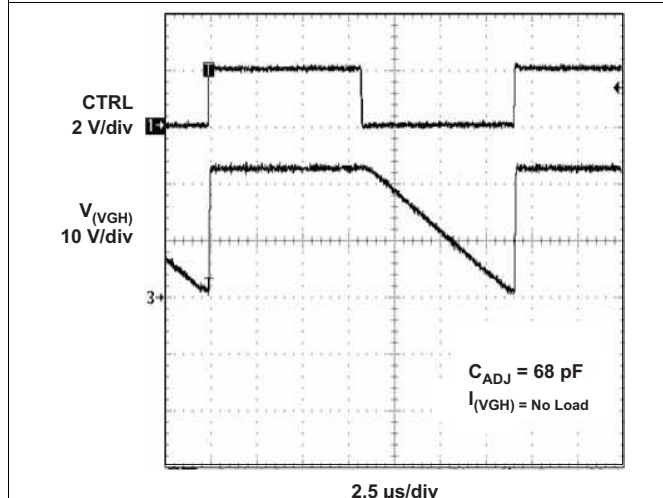


图 28. Gate Voltage Shaping

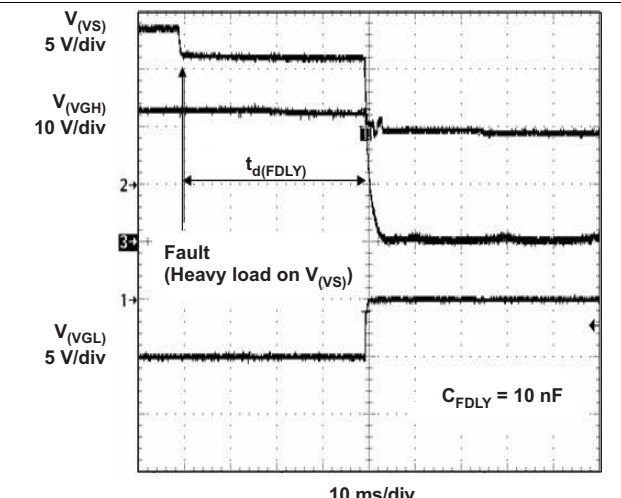


图 29. Adjustable Fault Detection Time

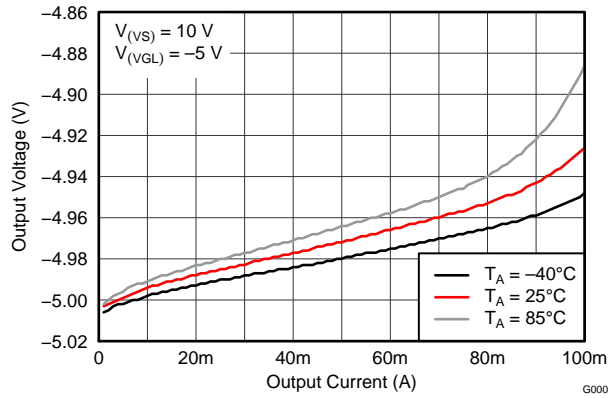


图 30. Negative Charge Pump Load Regulation

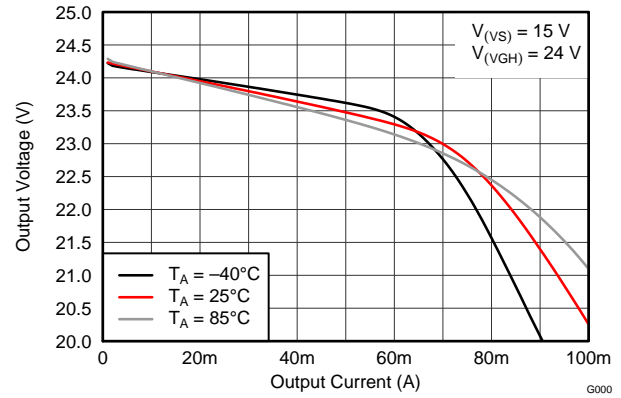


图 31. Positive Charge Pump Load Regulation (x2)

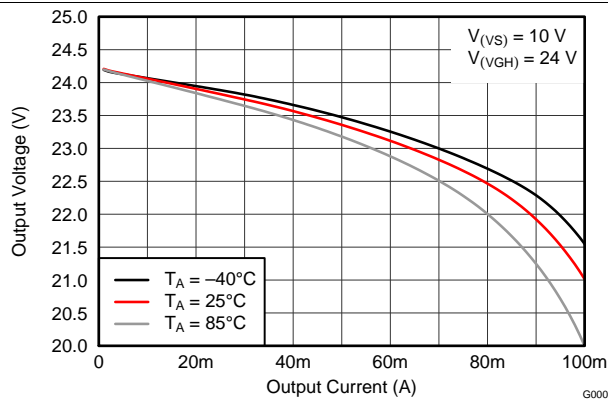


图 32. Positive Charge Pump Load Regulation (x3)

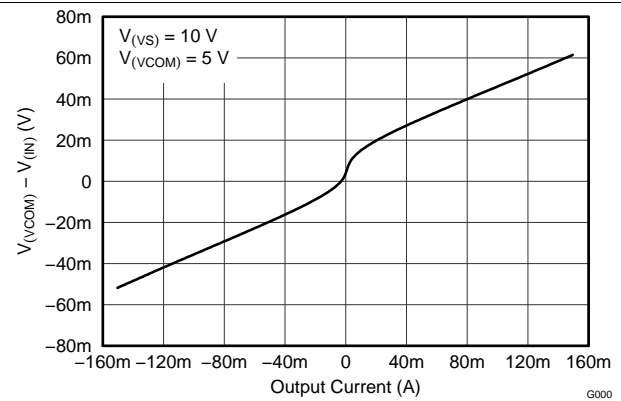


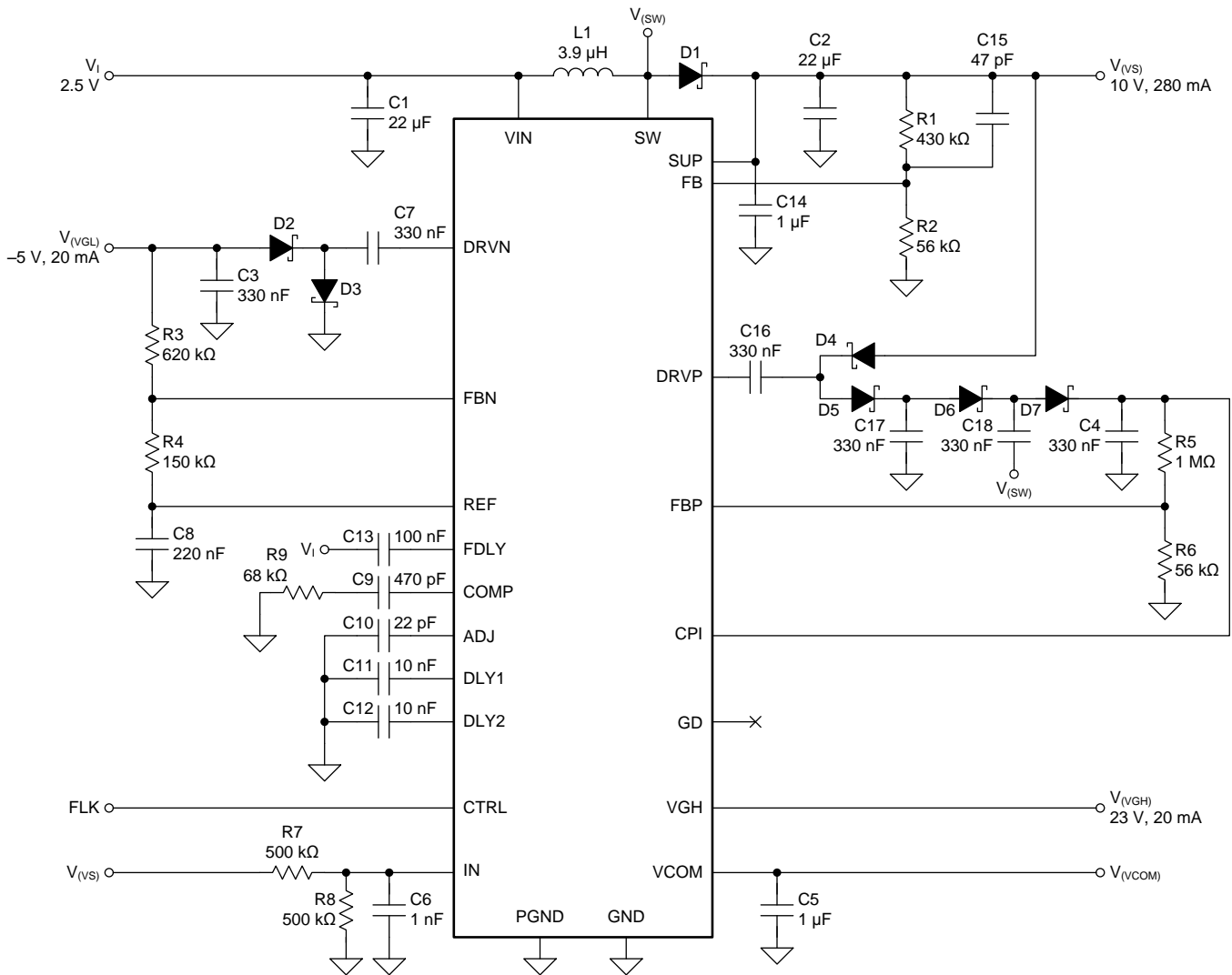
图 33. VCOM Buffer Load Regulation

TPS65150-Q1

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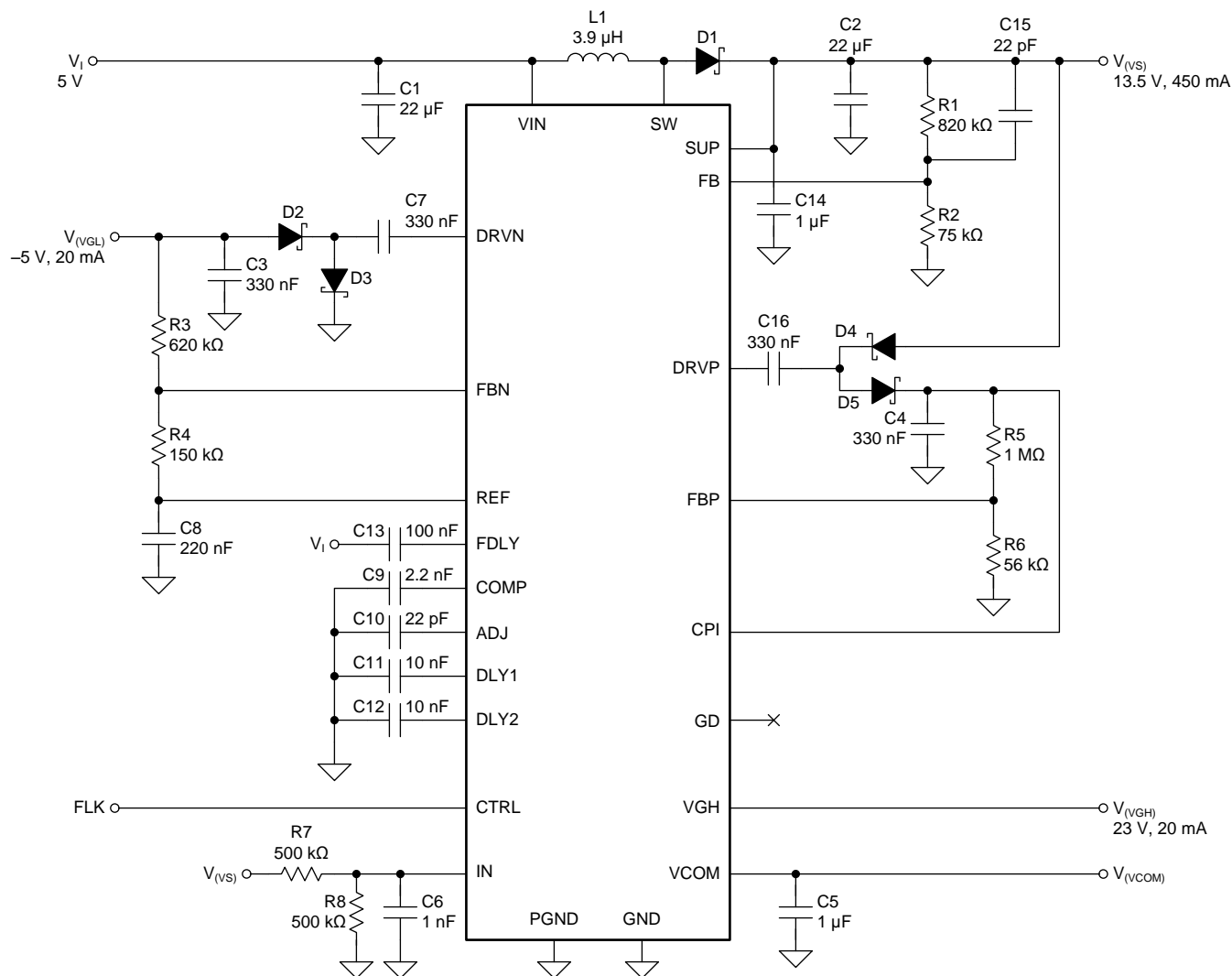
8.3 System Examples



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图 34. Notebook LCD Supply Powered from a 2.5-V Rail

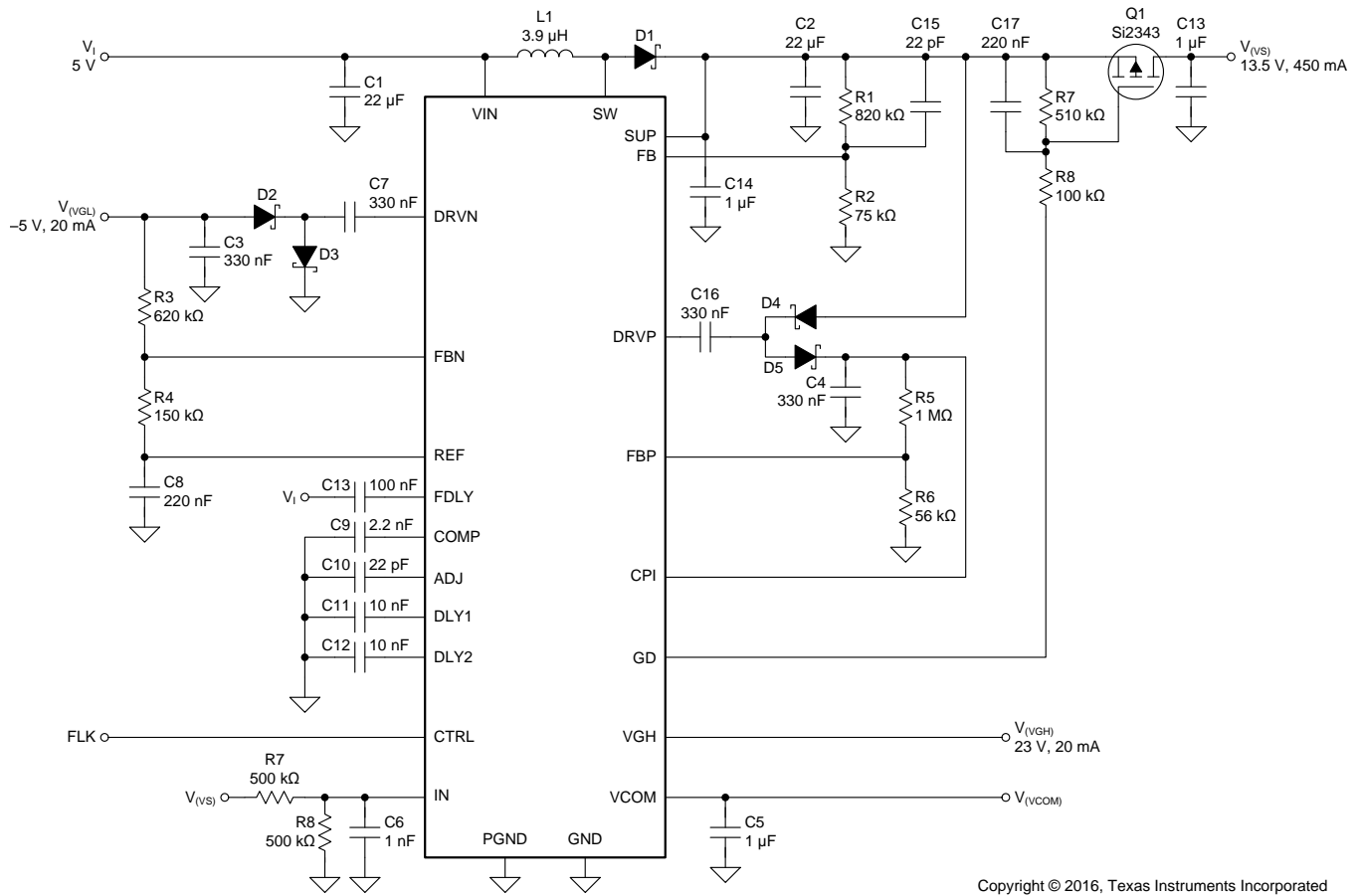
System Examples (接下页)



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图 35. Monitor LCD Supply Powered from a 5-V Rail

System Examples (接下页)



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图 36. Typical Isolation and Short Circuit Protection Switch for V(Vs) Using Q1 and Gate Drive Signal (GD)



## 9 Power Supply Recommendations

The TPS65150-Q1 device is designed to operate with input supplies from 1.8 V to 6 V. Like most integrated circuits, the input supply must be stable and free of noise if the full performance of the device is to be achieved. If the input is placed more than a few centimeters away from the device, additional bulk capacitance may be required. The input capacitance shown in the application schematics in this data sheet is sufficient for typical applications.

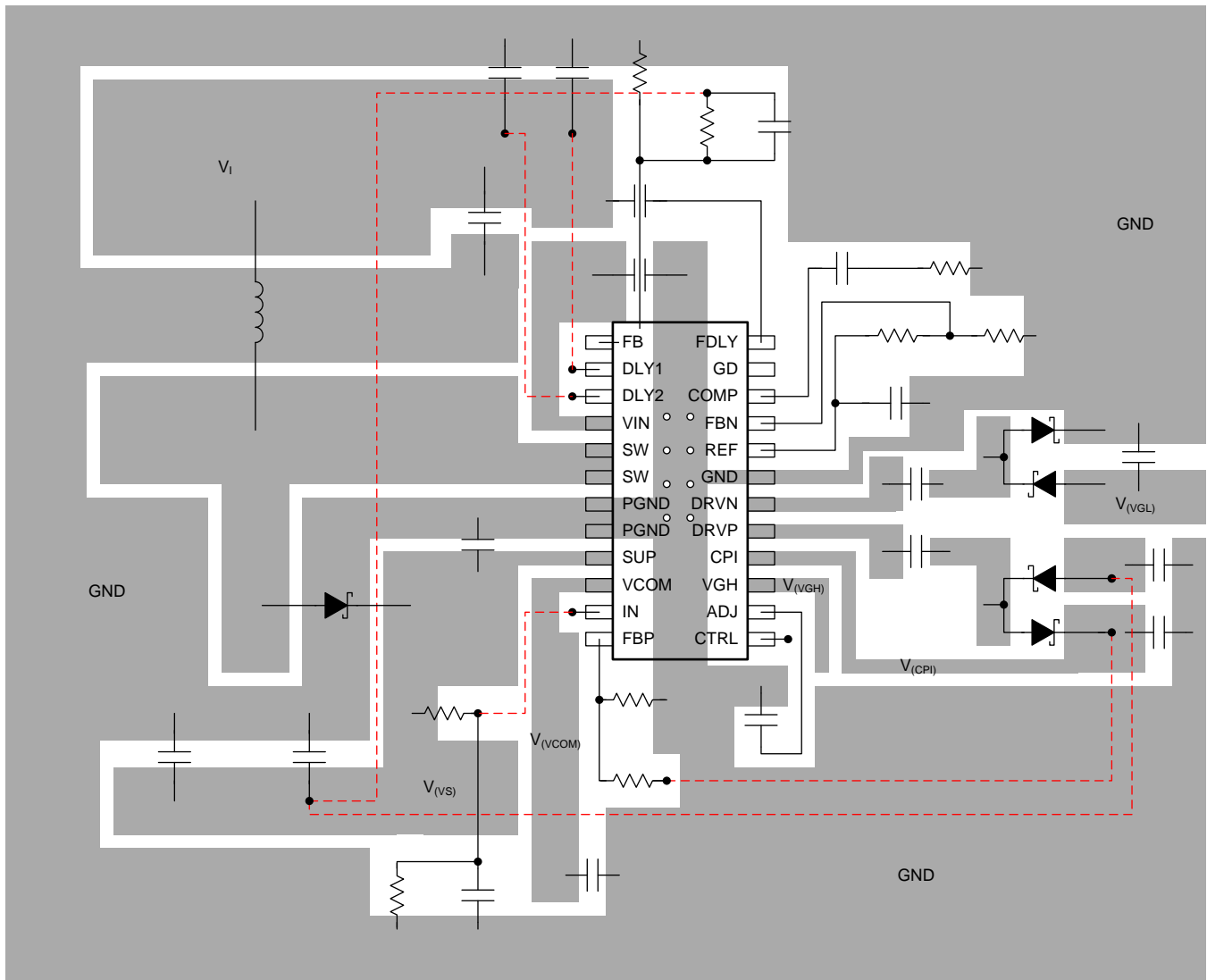
## 10 Layout

### 10.1 Layout Guidelines

The PCB layout is an important step in the power supply design. An incorrect layout could cause converter instability, load regulation problems, noise, and EMI issues. Especially with a switching DC-DC converter at high load currents, too-thin PCB traces can cause significant voltage spikes. Good grounding is also important. If possible, TI recommends using a common ground plane to minimize ground shifts between analog ground (GND) and power ground (PGND). Additionally, the following PCB design layout guidelines are recommended for the TPS65150-Q1 device:

1. Boost converter output capacitor, input capacitor and Power ground (PGND) must form a star ground or must be directly connected together on a common power ground plane.
2. Place the input capacitor directly from the input pin (VIN) to ground.
3. Use a bold PCB trace to connect SUP to the output Vs.
4. Place a small bypass capacitor from the SUP pin to ground.
5. Use short traces for the charge-pump drive pins (DRVN, DRVP) of VGH and VGL because these traces carry switching currents.
6. Place the charge pump flying capacitors as close as possible to the DRVP and DRVN pin, avoiding a high voltage spikes at these pins.
7. Place the Schottky diodes as close as possible to the device and to the flying capacitors connected to DRVP and DRVN.
8. Carefully route the charge pump traces to avoid interference with other circuits because they carry high voltage switching currents .
9. Place the output capacitor of the VCOM buffer as close as possible to the output pin (VCOM).
10. The thermal pad must be soldered to the PCB for correct thermal performance.

## 10.2 Layout Example



- Via to inner / bottom signal layer
- Thermal via to copper pour on inner / bottom signal layer

图 37. PCB Layout Example

## 11 器件和文档支持

### 11.1 器件支持

#### 11.1.1 Third-Party Products Disclaimer

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#### 11.6 Glossary

**SLYZ022** — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 机械、封装和可订购信息

以下页面包括机械、封装和可订购信息。这些信息是指定器件的最新可用数据。这些数据发生变化时，我们可能不会另行通知或修订此文档。如欲获取此产品说明书的浏览器版本，请参阅左侧的导航栏。

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS65150QPWRQ1	ACTIVE	HTSSOP	PWP	24	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	TPS65150Q	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION



### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS65150QPWPRQ1	HTSSOP	PWP	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS65150QPWPRQ1	HTSSOP	PWP	24	2000	350.0	350.0	43.0

## GENERIC PACKAGE VIEW

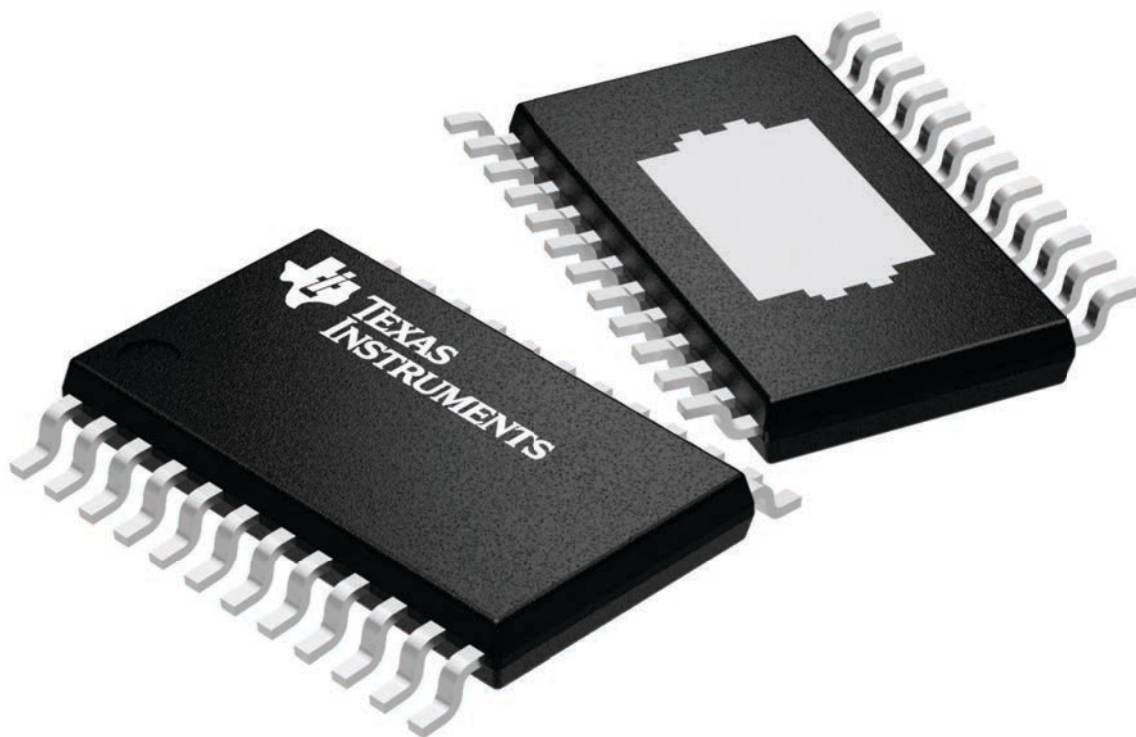
**PWP 24**

**PowerPAD™ TSSOP - 1.2 mm max height**

4.4 x 7.6, 0.65 mm pitch

PLASTIC SMALL OUTLINE

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

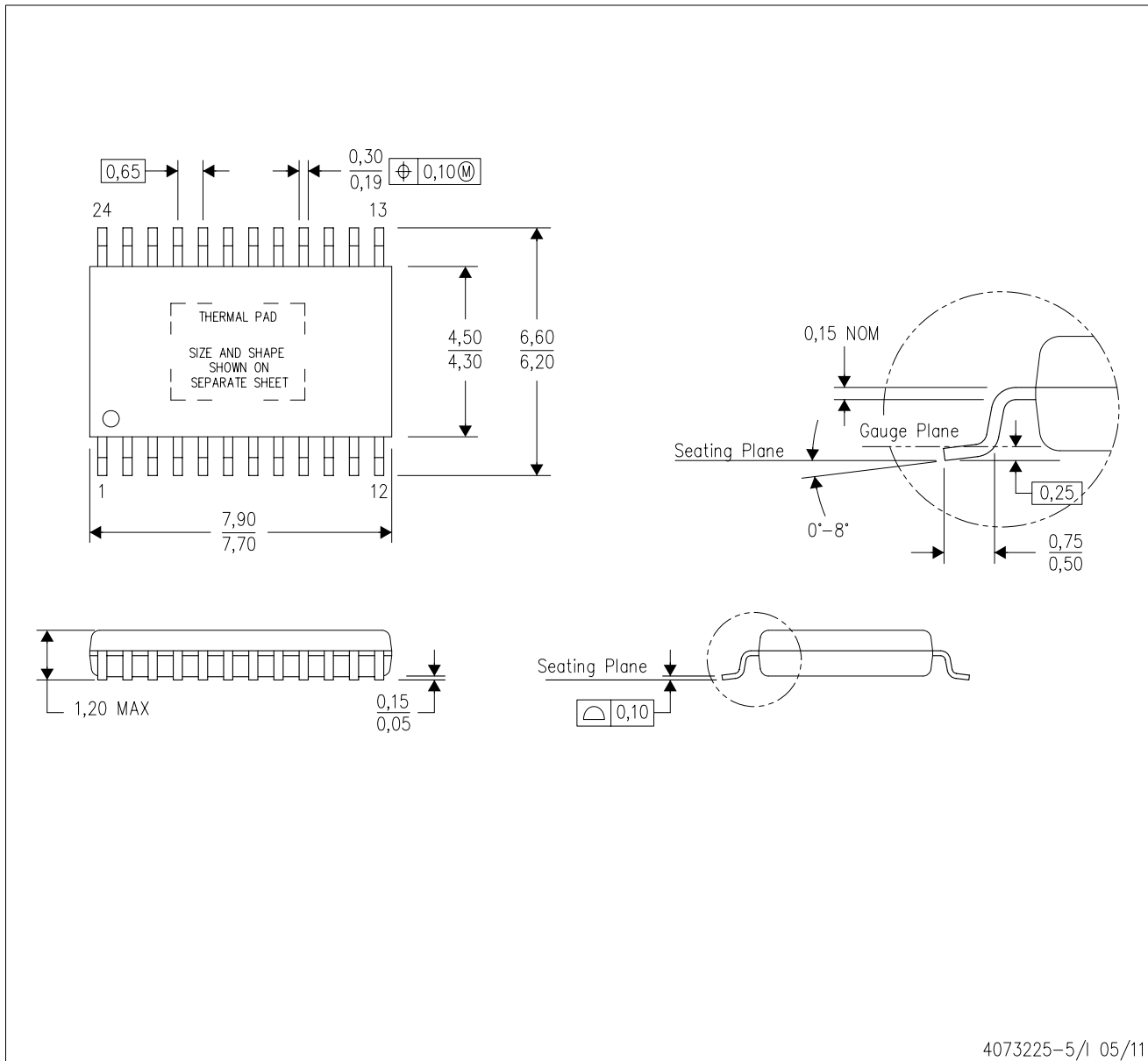


4224742/B

# MECHANICAL DATA

PWP (R-PDSO-G24)

PowerPAD™ PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
  - This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at [www.ti.com](http://www.ti.com) <<http://www.ti.com>>.
  - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
  - Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.



# THERMAL PAD MECHANICAL DATA

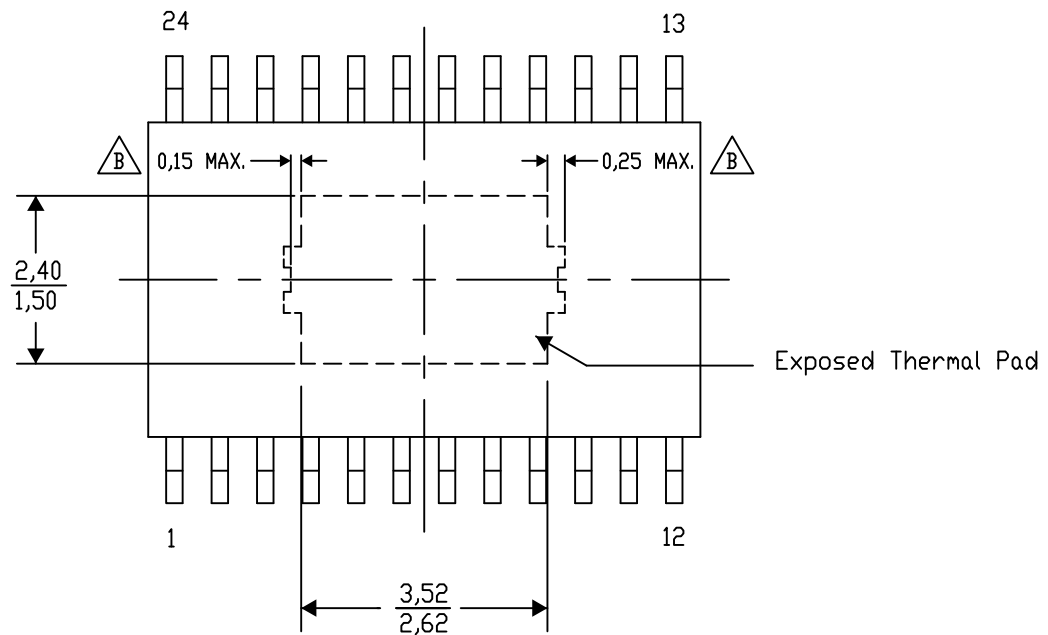
## PWP (R-PDSO-G24) PowerPAD™ SMALL PLASTIC OUTLINE

### THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at [www.ti.com](http://www.ti.com).

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

4206332-30/AO 01/16

NOTE: A. All linear dimensions are in millimeters

B. Exposed tie strap features may not be present.

PowerPAD is a trademark of Texas Instruments

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